

Supplementary Materials for

Improved compactness of self-assembled monolayers through Coulomb interaction enables highly efficient and stable perovskite solar cells

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Materials and Methods

Materials: Nickel nitrate hexahydrate ($\text{Ni}(\text{NO}_3)_2 \cdot 6\text{H}_2\text{O}$, 99.999%), chlorobenzene (CB, 99.8%), anhydrous dimethyl sulfoxide (DMSO, 99.8%), and N,N-dimethylformamide (DMF, 99.8%) were purchased from Sigma-Aldrich. Lead iodide (PbI_2), cesium iodide (CsI), methylammonium iodide (MAI), lead bromide (PbBr_2), bathocuproine (BCP), and methylamine hydrochloride (MAH) were purchased from Xi'an Yuri Solar Co. Ltd. Phenethylammonium bromide (PEABr), formamidinium iodide (FAI) were purchased from Greatcell Solar Materials. Lithium hydroxide (LiOH, 99.99%), sodium hydroxide (NaOH, 99.9%), and potassium hydroxide (KOH, 99.99%) were purchased from Aladdin. [4-(3,6-dimethyl-9H-carbazol-9-yl)butyl]phosphonic acid (Me-4PACz), [2-(9H-carbazol-9-yl)ethyl] phosphonic acid (2PACz), and [4-(3,6-dimethoxy-9H-carbazol-9-yl)butyl]phosphonic acid (MeO-4PACz) were obtained from TCI America.

Materials Synthesis: Nickel oxide nanoparticles (NiO_x -NPs) were synthesized according to a previous literature¹. 1.7 M $\text{Cs}_{0.05}\text{MA}_{0.05}\text{FA}_{0.9}\text{PbI}_3$ perovskite precursors were prepared by dissolving 0.085 mmol CsI, 0.085 mmol MAI, 1.53 mmol FAI, and 1.7 mmol PbI_2 in DMF: DMSO (4:1 volume ratio, v: v), 5% MAPbCl_3 excess were added to improve the quality of perovskite films. The precursor solutions were stirred at 60 °C for 1 h and then filtered using a 0.22 μm polytetrafluoroethylene membrane before use.

Inverted (p-i-n) Solar Cell Fabrication: ITO glasses were continuously washed in an ultrasonic bath for 15 min in detergent-deionized water solution, acetone and ethanol, respectively. The ITO glasses were dried with N_2 and then treated with UV-ozone for 7 min to increase hydrophilicity. NiO_x -NPs (20 mg mL^{-1} in H_2O) was deposited on ITO at 2000 rpm for 30 s and then heated at 100 °C for 10 min. The coated ITO was then moved to a glove box. The LiOH-reacted Me-4PACz were fabricated by spin-coating the Me-4PACz (0.3 mg mL^{-1} in $\text{C}_2\text{H}_5\text{OH}$) and LiOH (molar ratio=1:0, 1:0.25, 1:0.5, 1:1, 1:2) on NiO_x -NPs substrates at 4000 rpm for 30 s, followed by thermal annealing at 100 °C for 10 min. After that, the substrates needed to be washed

with ethanol through spin-coating at 4000 rpm for 30 s, then annealing at 100 °C for 5 min. The perovskite solution was spin coated on the Me-4PACz or LiOH-reacted Me-4PACz according to procedure that was increased from 1000 rpm for 10 s to 5000 rpm for 30 s, dropping 150 μ L chlorobenzene antisolvent for 10 s before the end of the procedure. Then heated at 110 °C for 10 min to obtain the bright perovskite film. PEABr with concentration of 1 mg/ml in IPA and DMSO solution (volume ratio 200:1) was dynamically spin-coated on top (4000 rpm, 30 s) and annealed at 100 °C for 5 min. After that, the PCBM and C₆₀ mixed solution (25 mg mL⁻¹, 4/1, w/w, 1mL CB) was spin-coated on the PEABr at speed of 3000 rpm for 30 s. Next, BCP (0.5 mg mL⁻¹ in IPA) was spin coated on it at 5000 rpm for 30 s. Finally, fabrication of the devices was accomplished by thermally evaporating Ag (100 nm) electrodes (0.0535 cm² mask area). A 100-nm thick magnesium fluoride layer was deposited on the back of ITO substrate for transmittance enhancement.

Solar Cell Characterization: The SEM images of perovskite films and cross-sectional devices were obtained using Tescan MAIA3. GIXRD patterns of the perovskite films were gained by using Rigaku SmartLab 9kW. The crystallization of the perovskite film was characterized via grazing-incidence wide-angle X-ray scattering (GIWAXS, BL14B1 beamline of the Shanghai Synchrotron Radiation Facility (SSRF) using X-ray with a wavelength of 0.6887 Å). XPS and UPS measurements were obtained on a Thermo Fisher Scientific Nexsa. The *J-V* curves of PSCs were recorded under AM 1.5 G (100 mW cm⁻²) solar illumination from a Elitetechn solar simulator, and the scan rate corresponding to the curve was 0.02 V s⁻¹. EQE spectra of the PSCs were obtained from ZOLIX Optoelectronic Device Quantum Efficiency Measurement. FT-IR spectra were measured on a Jasco FT-IR-6100 in a wavelength range of 4000 to 650 cm⁻¹. Admittance spectroscopy (AS) was conducted using an impedance analyzer (ZAHNER Stat.). Mott-Schottky analysis was carried out on an electrochemical workstation (Chenhua 760) and was measured in the 0-1.5 V voltage range and 1000 Hz frequency under dark. KPFM and AFM were conducted

with an Asylum Research AFM (OXFORD). TOF-SIMS of films were analyzed using a TOF-SIMS5-100 with the sputter ion of 5 k eV Cs⁺ cluster. The PL spectra of perovskite samples were obtained via spectrometer (FLS980) at an emission laser of 510 nm. The TRPL measurements were carried out via the PicoQuant FluoQuant 300. TPV and TPC measurements were done on a home-made system. A white light bias on the sample was generated from an array of diodes. Red light pulse diodes (0.05s square pulse width, 100 ns rise and fall time) controlled by a fast solid-state switch were used as the perturbation source. The transient photocurrent was measured using 20-ohm external series resistance to operate the device in short circuit. Similarly, transient photovoltage was measured using 1 M Ω external series resistance to operate the device in open circuit. The voltage dynamics on the resistors were recorded on a digital oscilloscope (Tektronix MD03032). The perturbation red light source was set to a suitably low level to the white diodes array with light intensity equivalent to 100 mW cm⁻² of a standard solar simulator.

Stability Test: The complete PSCs could be encapsulated in a N₂ glove box with a cover glass and UV adhesive. The operational stability of the encapsulated cells was measured at 65 °C/85 °C under a white light emitting diode lamp with sixteen-channel thin film photovoltaic maximum power point tracking test system (YH-VMPP-16). To improve the stability of the device, we replaced the Ag electrode with a Cr/Au electrode and used C₆₀ as electron transport layer. The thermal stability of the non-encapsulated solar cells was implemented under 85°C thermal pressure and in a N₂ glove box. The PCEs of the devices were periodically obtained under AM 1.5 G simulated sun light illumination in ambient air.

Density Functional Theory (DFT) Calculations: The dipole moments, HOMO, LUMO, and electrostatic potential were performed using the ORCA 6.0.0 at the B3LYP-D3(BJ)/def2-TZVP level ². The surface adsorption behaviors of SAM molecules (Me-4PACz and Me-4PACz-Li) on NiO surface were analyzed using a plane wave (PW) basis and the projector-augmented wave (PAW) pseudopotentials, as

implemented in the Vienna Ab initio Simulation Package (VASP) ³. The adsorption structures of SAM molecules on the crystal surface were constructed following the methods as described in Ref. ⁴. The generalized gradient approximation (GGA) with Perdew-Burke-Ernzerhof (PBE) functional was employed for the exchange-correlation potential, and long-range dispersion interactions were corrected using DFT-D3 method ⁵. The energy cutoff was set at 520 eV for the wave functions, with convergence thresholds for energy and atomic force were set to 1×10^{-5} eV and 0.02 eV/Å, respectively. Following Ref.⁴, Hubbard corrections for Ni were set as $U = 8$ eV and $J = 0.95$ eV. The slab structures of NiO were built by a 3×3 lateral periodicity, exposing the (100) surface to ~ 25 Å of vacuum to prevent interactions between slab replicas. The binding energy between SAM molecule and NiO slab was calculated as $E_{\text{binding}} = E_{\text{system}} - E_{\text{SAMs}} - E_{\text{slab}}$, where E_{system} is the energy of the whole system upon adsorption of SAM molecules, E_{SAMs} and E_{slab} are the energies of isolated SAM molecule and the NiO slab structure, respectively.

Molecular Dynamics (MD) Simulations: The dispersion behavior of Me-4PACz-Li molecules on the NiO substrate was investigated using classical MD simulations in LAMMPS ⁶, following the methods outlined in Ref.^{7,8}. The NiO substrate was generated by the $24 \times 24 \times 3$ supercell of NiO, producing a slab model with dimensions of approximately $100 \times 100 \times 12.6$ Å³. The SAM layers, with a thickness of 18 Å, were constructed by randomly placing the Me-4PACz and Me-4PACz-Li molecules above the substrate using the Packmol software ⁹. The distance between SAM layer and the NiO substrate was maintained at 4.8 Å. The simulation models were created with 6 different fractions of Me-4PACz-Li (*i.e.*, Me-4PACz: Me-4PACz-Li = 1:0, 0.9:0.1, 0.75:0.25, 0.5:0.5, 0.25:0.75, and 0:1), while the total number of SAM molecules was kept at 200. The interactions within SAM molecules were described using the OPLS-AA force field ¹⁰, which has been widely used in simulating the aggregation of SAM molecules. The atomic charges of the SAM molecules were determined using the restrained electrostatic potential charges computed from ORCA

6.0.0 at the B3LYP-D3(BJ)/def2-TZVP level ². The interactions within NiO substrate were described using the INTERFACE potential ¹¹, which has shown good promise in reproducing the molecular adsorption behavior on various metal oxides. The interactions between SAM molecules and NiO substrate were described by Lennard-Jones potential using the geometric mixing rule. Long-range Coulombic interactions were calculated using the Particle-Particle Particle-Mesh (PPPM) method with an accuracy of 10^{-5} . The simulation models were dynamically equilibrated at 300 K in the canonical ensemble (NVT) for 1 ns. The motion of atoms was described using the velocity Verlet integration with a time step of 1 fs, and periodic boundary condition was applied in all directions. The surface coverage of SAM molecules on the substrate was quantified by constructing a surface mesh using the method implemented in the Ovito software ¹², which was also used for visualizing the simulated structures. The interfacial interactions between SAM molecules and NiO substrate were estimated by calculating the adsorption energy as $E_{\text{inter}} = E_{\text{total}} - E_{\text{SAMs}} - E_{\text{NiO}}$, where E_{total} , E_{SAMs} , and E_{NiO} are the potential energy of the whole system, SAM molecules, and NiO substrate, respectively. The calculated E_{inter} is normalized by the number of SAM molecules (200).

Supplementary Note 1

The surface coverage of SAM was calculated using the formula

$$\Gamma = \frac{A(\lambda)}{1000\varepsilon(\lambda)} \quad (1)$$

where Γ is the surface coverage (mol cm^{-2}), $A(\lambda)$ is the absorbance of the SAM and $\varepsilon(\lambda)$ is the molar extinction coefficient of SAM molecule ¹³. The $\varepsilon(\lambda)$ value of $5.53 \times 10^3 \text{ M}^{-1} \text{ cm}^{-1}$ for Me-4PACz and LiOH-reacted Me-4PACz at their absorption maximum in DMF.

Supplementary Note 2

CV measurements were conducted using a three-electrode configuration. The working electrodes were prepared using a spin coating method on an ITO electrode. The exposed area of the working electrode to the electrolyte measures $15 \text{ mm} \times 12 \text{ mm}$. A platinum plate and an Ag/AgCl electrode (in a 3.0 M KCl solution) were employed

as the counter and reference electrodes, respectively. The measurements were performed in an Ar-saturated solution of 1,2-dichlorobenzene (o-DCB) with 0.1 M tetrabutylammonium hexafluorophosphate ($\text{TBA}^+\text{PF}_6^-$) serving as the supporting electrolyte. All potentials are referenced against the ferrocene redox couple, serving as an internal standard. The effective coverage of the SAMs on the ITO surface is measured by the slope of a linear dependency of the oxidative peak intensity against the scan rate as follows:

$$i_{p,o} = \frac{n^2 F^2}{4RTN_A} A \Gamma^* v \quad (2)$$

$i_{p,o}$ is the oxidative peak current, v is the voltage scan rate, n is the number of electrons transferred, F is the Faraday constant ($96485.33 \text{ C mol}^{-1}$), R is the universal gas constant ($8.314 \text{ J K}^{-1} \text{ mol}^{-1}$), T is the temperature, N_A is the Avogadro constant, A is the electrode area, and Γ^* is the areal density.

Supplementary Note 3

Change the φ (where φ is the angle of the diffraction vector with respect to the sample's normal direction) from 10° to 50° to get the relationship between the interplanar distance d_n and $\sin^2\varphi$. The residual stress in the perovskite film is estimated based on the slope of the d_n - $\sin^2\varphi$ fitting curve given by:

$$\sigma_R = \left(\frac{E}{1+\nu}\right)\left(\frac{m}{d_n}\right) \quad (3)$$

where σ_R is the residual stress of the film; E is the Young's modulus of the perovskite film (15 GPa); ν is the Poisson's ratio (0.3); m is the slope of the straight line after linear fitting; d_n is the intercept of the straight line after linear fitting.¹⁴ ↵

Supplementary Note 4

We fabricated hole-only devices (ITO/ NiO_x -NPs/Me-4PACz or LiOH-reacted Me-4PACz/perovskite film /PTAA /Ag) and evaluated the effect of LiOH-reacted Me-4PACz on defect state density and carrier mobility using the space charge limited

current (SCLC) method. The low-bias region is the ohmic region, the middle-bias region is the defect filling limit region, and the high-bias region is the SCLC region. The defect filling limit voltage (V_{TFL}) is determined at the junction of the low and middle bias regions, and the defect density (N_t) is obtained using Eq. 4:¹⁵

$$N_t = \frac{2\varepsilon\varepsilon_0 V_{TFL}}{eL^2} \quad (4)$$

where ε_0 and ε are the vacuum and relative permittivity, e is the electron charge, and L is the film thickness.

According to the Mott-Gurney law in Eq. 5, the carrier mobility (μ) can be calculated from the Child region:¹⁶

$$\mu = \frac{8}{9} \frac{J}{\varepsilon\varepsilon_0} \frac{L^3}{V^2} \quad (5)$$

Supplementary Note 5

The hysteresis factor (HF) is quantified as:

$$HF = \frac{PCE_{reverse} - PCE_{forward}}{PCE_{reverse}} \quad (6)$$

Supplementary Note 6

The carrier recombination mechanism was determined by studying the dependence of V_{OC} of PSCs on the incident light intensity (I) using Eq. 7:

$$V_{OC} = \frac{nk_B T}{q} \ln(I) \quad (7)$$

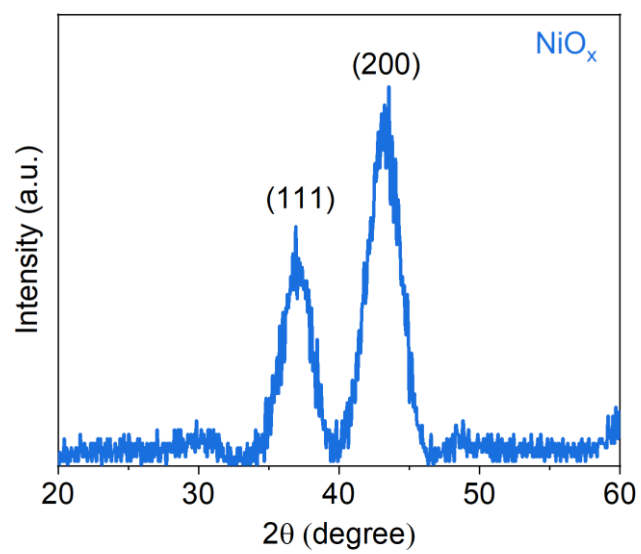
where n is the ideality factor, k_B is the Boltzmann constant, and T is the temperature.

Supplementary Note 7

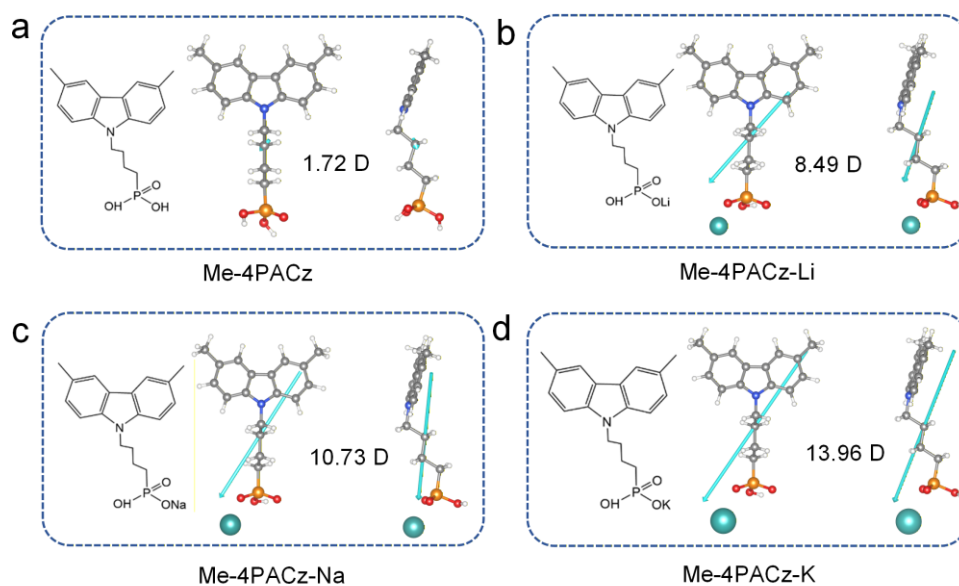
Admittance spectroscopy (AS)¹⁷

AS is an effective technique for estimating both the energy level of trap states and the distribution of trap state density, which has been extensively applied to many photovoltaic systems, such as organic solar cells, $\text{Cu}_2\text{ZnSnS}_4$ solar cells, and PSCs. As the literature reported, for a p-type perovskite semiconductor, the defect activation energy (E_a) is approximately the depth of the trap state energy level (E_T) relative to the

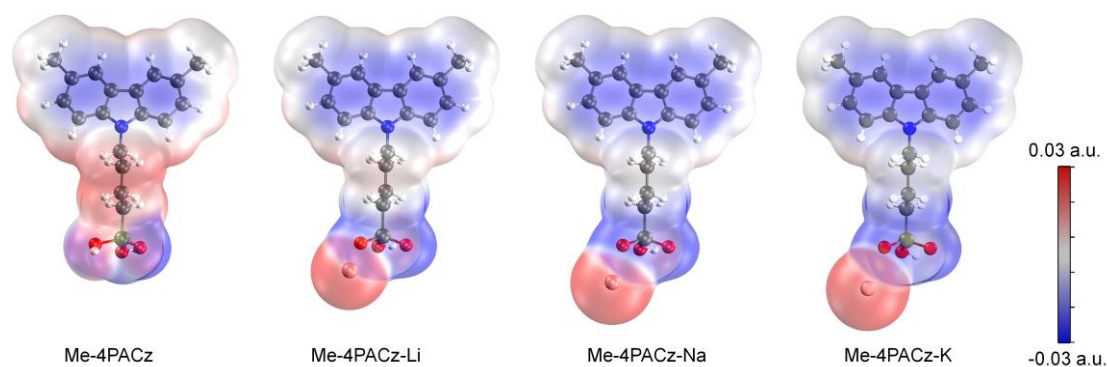
valence band maximum (VBM) energy level (E_{VBM}) of perovskite ($E_a = E_T - E_{\text{VBM}}$). E_a and the characteristic transition angular frequency (ω_0) can be expressed in the relation $\omega_0 = \beta T^2 \exp(-\frac{E_a}{k_B T})$, where β is a temperature dependent parameter, T is the temperature and k_B is the Boltzmann's constant. The ω_0 is determined by the derivative of the capacitance–frequency spectrum. According to this equation, the Arrhenius plot ($\ln(\frac{\omega_0}{T^2}) = \ln \beta - \frac{E_a}{k_B T}$), and the value of E_a can be obtained from the slope of the Arrhenius plot line. The distribution of trap state density can be derived from the equation, $N_T(E_\omega) = -\frac{V_{bi}}{qW} \frac{dC}{d\omega} \frac{\omega}{k_B T}$, $E_\omega = k_B T \ln(\frac{\omega_0}{\omega})$, where V_{bi} is the built-in potential, W is the depletion width, q is the elementary charge, C is the capacitance, and ω is the applied angular frequency. V_{bi} and W can be extracted from the Mott–Schottky analysis through the capacitance-voltage measurement. According to the depletion approximation, the C , V_{bi} , and W at the junction can be expressed in the relation, $\frac{C}{A} = \frac{\epsilon \epsilon_0 N}{W} = \sqrt{\frac{q \epsilon \epsilon_0 N}{2(V_{bi} - V)}}$, where A is active area, ϵ is the static permittivity of perovskite, ϵ_0 is the permittivity of free space, N is the apparent doping profile in the depleted layer, and V is the applied bias. A Mott-Schottky plot ($\frac{A^2}{C^2} = \frac{2(V_{bi} - V)}{q \epsilon \epsilon_0 N}$) describes a straight line where the intersection on the bias axis determines V_{bi} and the slope gives the impurity doping density N . Then, the depletion width $W = \sqrt{\frac{2 \epsilon \epsilon_0 V_{bi}}{qN}}$ corresponding to the zero bias can be calculated.



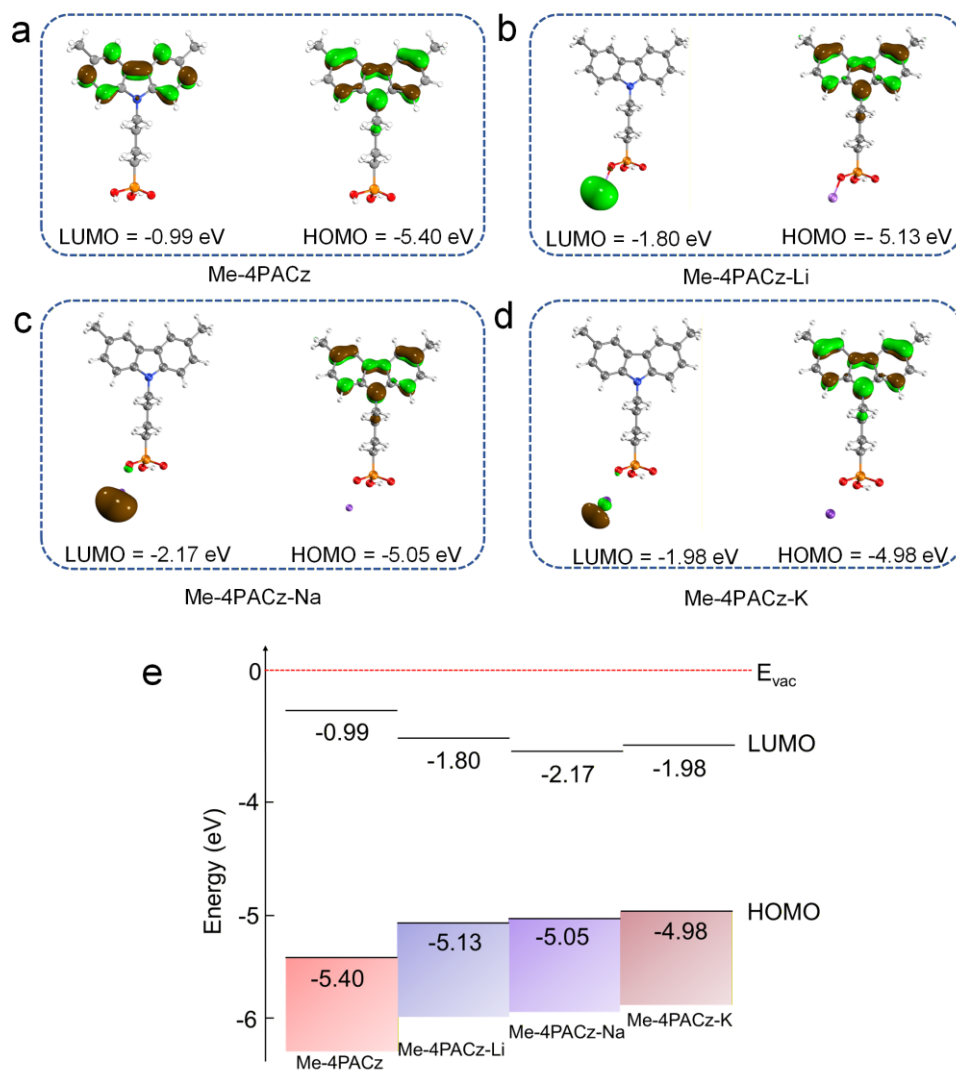
Supplementary Fig. 1 | The XRD pattern of NiO_x-NPs.



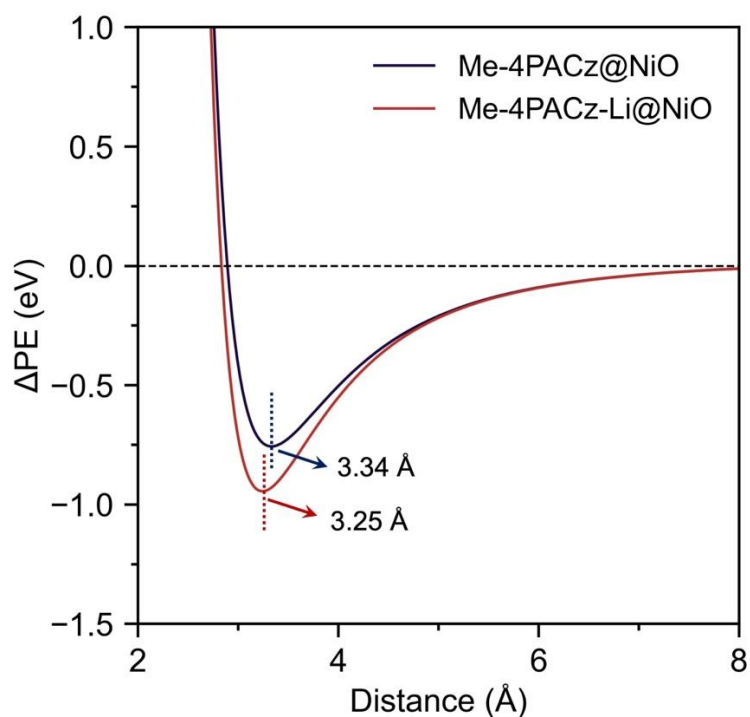
Supplementary Fig. 2 | Structures and dipole moments of SAM molecules. Molecular structures and calculated dipole moments (μ) of (a) Me-4PACz, (b) Me-4PACz-Li, (c) Me-4PACz-Na, and (d) Me-4PACz-K.



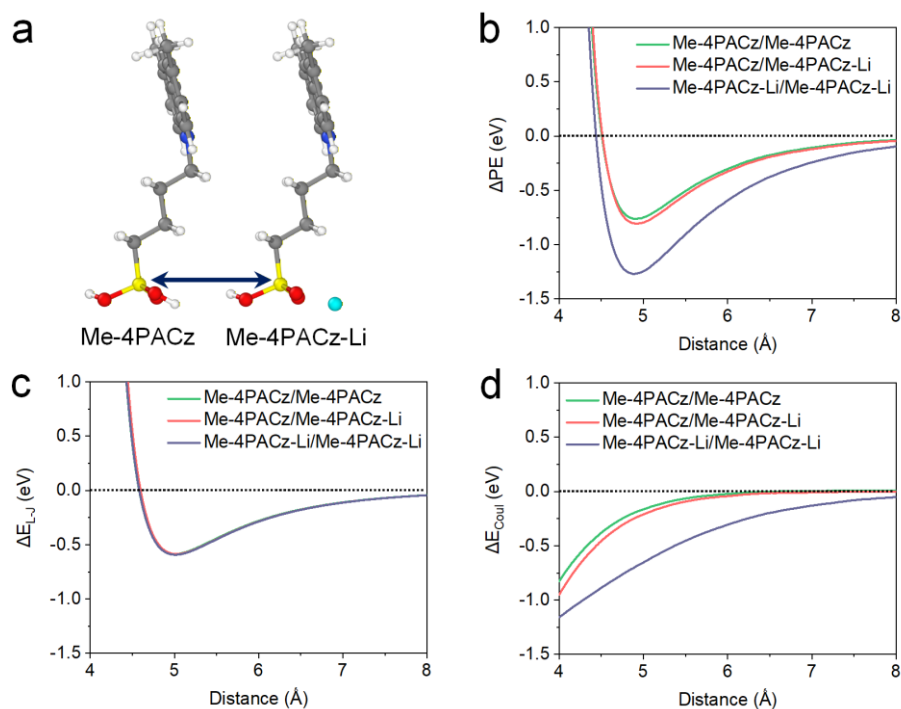
Supplementary Fig. 3 | Calculated electrostatic potential of SAMs. Electrostatic potential (ESP) distribution of Me-4PACz, Me-4PACz-Li, Me-4PACz-Na, and Me-4PACz-K molecules from DFT calculations, where the blue and red clouds represent the electron-rich and electron-poor regions, respectively.



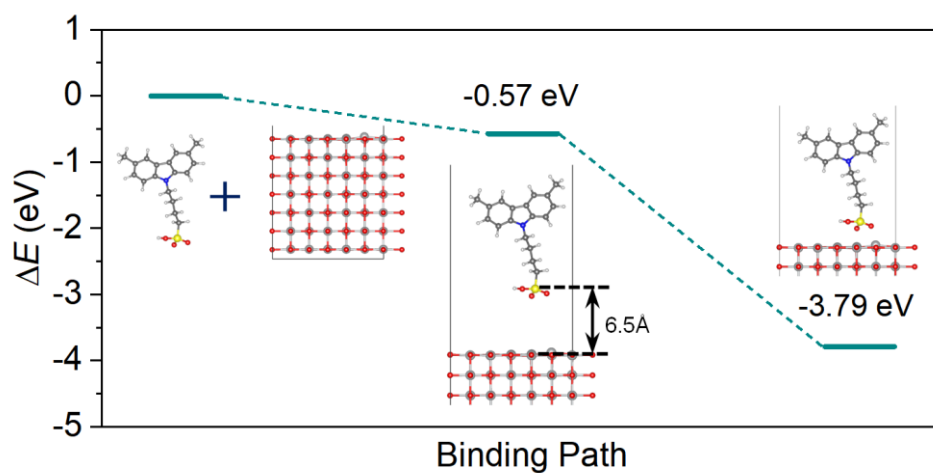
Supplementary Fig. 4 | Calculated energy levels of SAM molecules. Calculated LUMO and HOMO of (a) Me-4PACz, (b) Me-4PACz-Li, (c) Me-4PACz-Na, and (d) Me-4PACz-K. (e) Energy alignment of SAMs based on the calculated HOMO and LUMO levels.



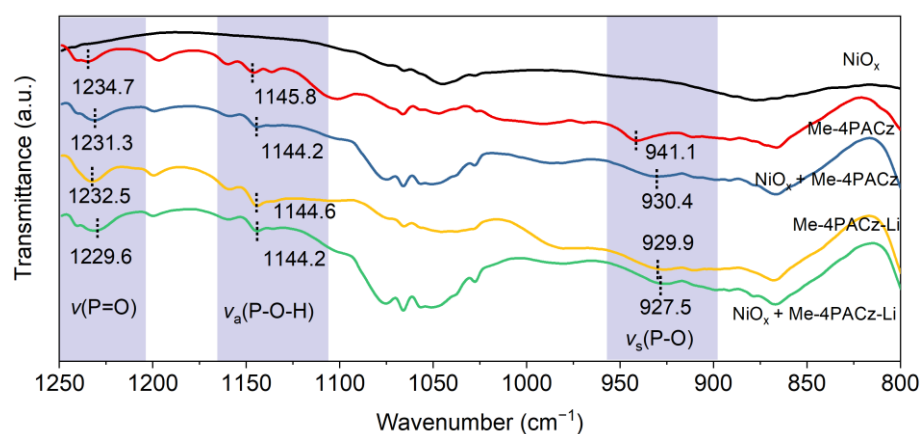
Supplementary Fig. 5 | Potential energy curves between SAM molecule and NiO substrate. The change in potential energy (ΔPE) for the two systems as a function of the distance in the z-direction between SAM molecule and NiO substrate. The distance is represented by the height of P atom relative to the NiO surface.



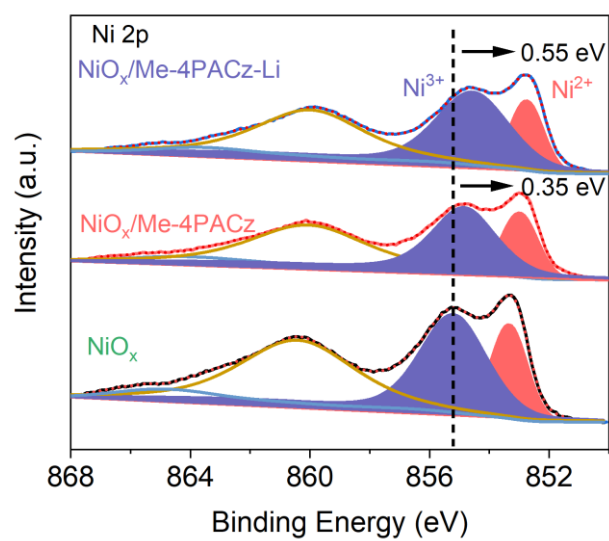
Supplementary Fig. 6 | Interactions between two SAM molecules as a function of the intermolecular distance, defined as the separation between two P atoms. (a) Schematic representation of the two SAM molecules. **(b)** Potential energy (ΔPE), and **(c–d)** the contributions from **(c)** Lennard-Jones and **(d)** Coulomb interactions.



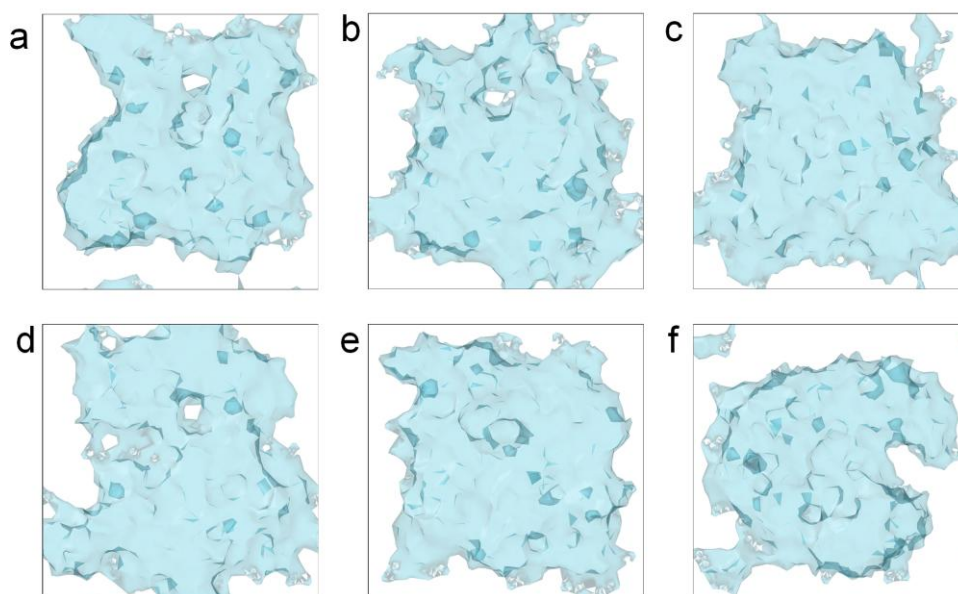
Supplementary Fig. 7 | Calculated potential energy of Me-4PACz⁻ on a NiO (100) surface with different distances. Change of potential energy along the binding path for Me-4PACz⁻ on the NiO (100) surface, obtained at GGA/PBE+U level with long-range dispersion interactions.



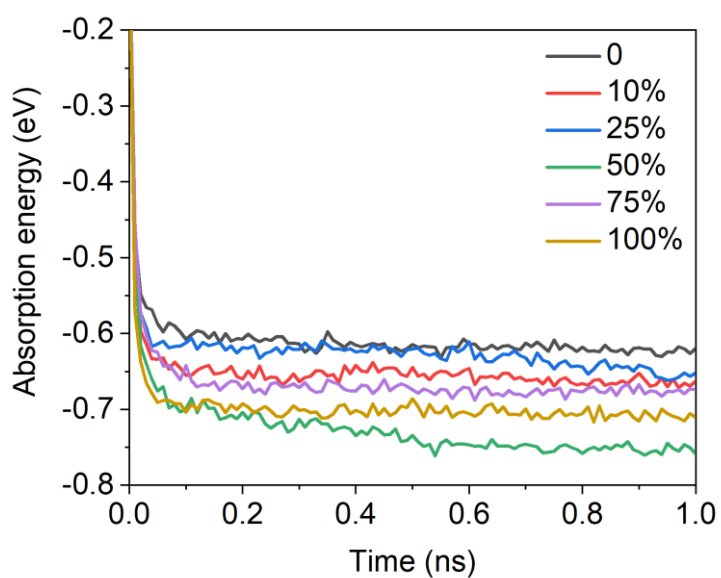
Supplementary Fig. 8 | FTIR characterization. FTIR spectra of NiO_x-NPs, Me-4PACz, Me-4PACz+NiO_x-NPs, Me-4PACz-Li, and Me-4PACz-Li+NiO_x-NPs films.



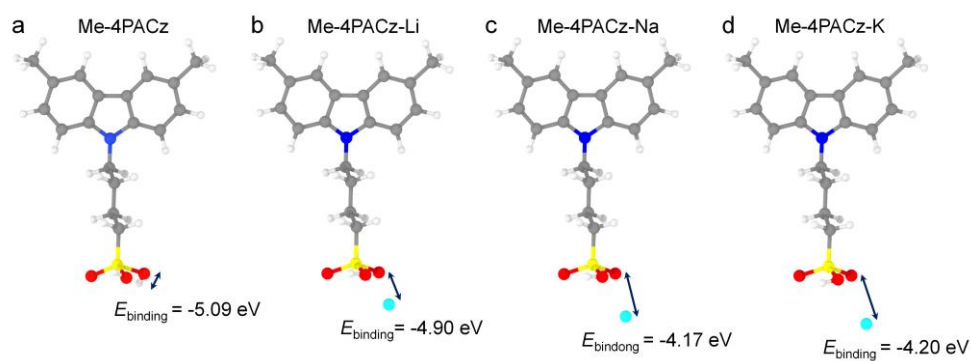
Supplementary Fig. 9 | XPS characterization. XPS spectra of Ni 2p for NiO_x-NPs, NiO_x-NPs/Me-4PACz, and NiO_x-NPs/Me-4PACz-Li films.



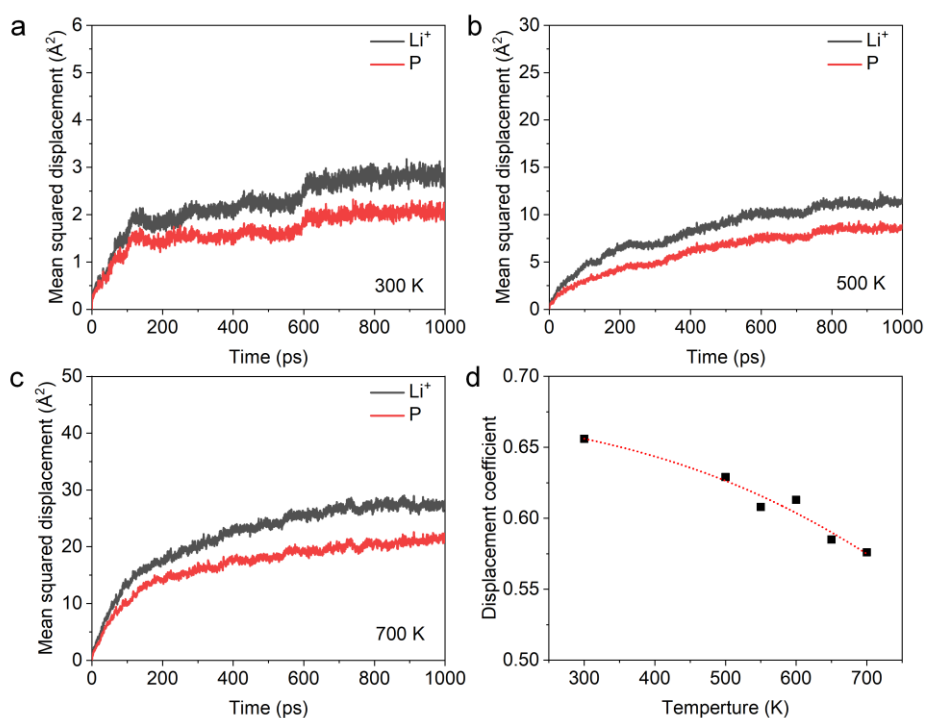
Supplementary Fig. 10 | Simulation of the coverage of different SAM molecules on NiO surfaces. Surface coverage of different SAM layers, including (a) pure Me-4PACz, (b) 90% Me-4PACz and 10% Me-4PACz-Li, (c) 75% Me-4PACz and 25% Me-4PACz-Li, (d) 50% Me-4PACz and 50% Me-4PACz-Li, (e) 25% Me-4PACz and 75% Me-4PACz-Li, and (f) pure Me-4PACz-Li on the NiO (100) substrate after 1 ns MD simulation (The size of the slab model is 10 nm x10 nm).



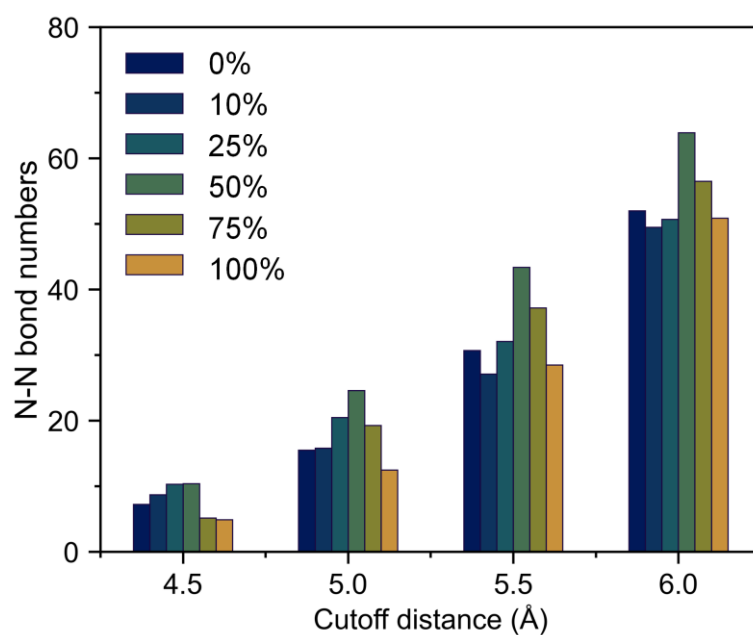
Supplementary Fig. 11 | Calculated adsorption energies of LiOH-reacted SAM molecules with different reaction ratios on NiO (100) surface over simulation time.



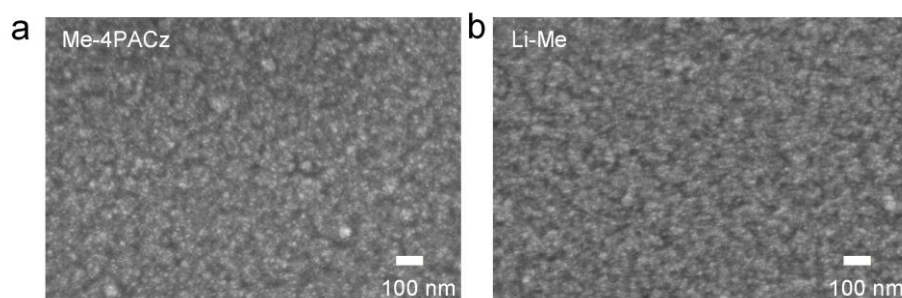
Supplementary Fig. 12 | The binding energies between H/alkali metal atoms and O atoms in the phosphate groups. Structures and corresponding binding energies between H/alkali metal atoms and O atoms in the phosphate groups of (a) Me-4PACz, (b) Me-4PACz-Li, (c) Me-4PACz-Na, and (d) Me-4PACz-K.



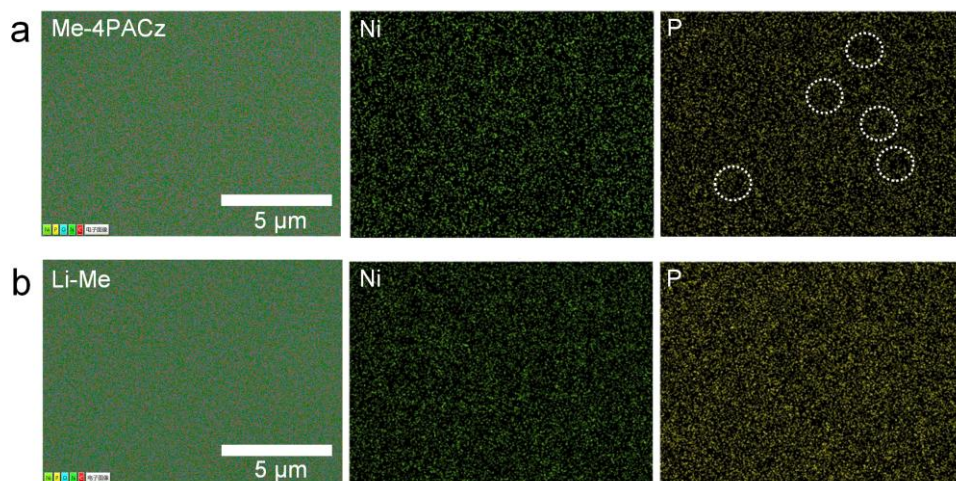
Supplementary Fig. 13 | Diffusion behavior of Li^+ and P within Me-4PACz-Li. Mean squared displacement of Li^+ and P at different temperatures: **(a)** 300 K, **(b)** 500 K, and **(c)** 700 K. **(d)** Displacement coefficient $C(t)$ between Li^+ and P as a function of temperatures. A value of $C(t)=1$ indicates that Li and P move in the same direction, $C(t) = -1$ indicates motion in opposite directions, and $C(t)=0$ corresponds to the absence of correlation.



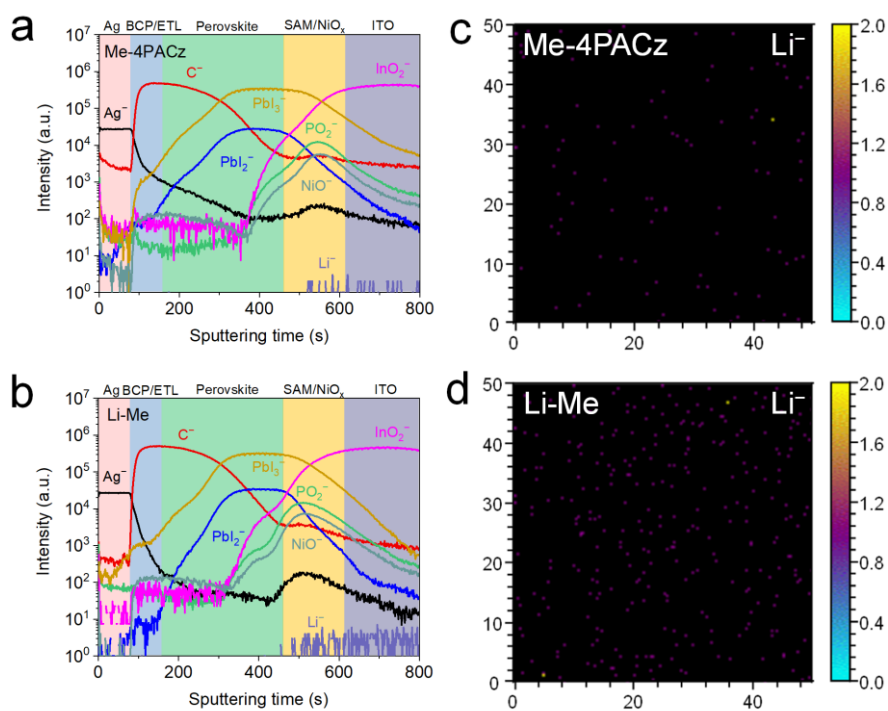
Supplementary Fig. 14 | The distribution of distances between neighboring SAM molecules to identify the compactness. The number of neighboring molecules with various distances within SAM layers adsorbed on NiO substrates after a 1 ns MD simulation. Li-Me shows the largest number of neighboring molecules with small distance, indicating the highest compactness of the SAM layer.



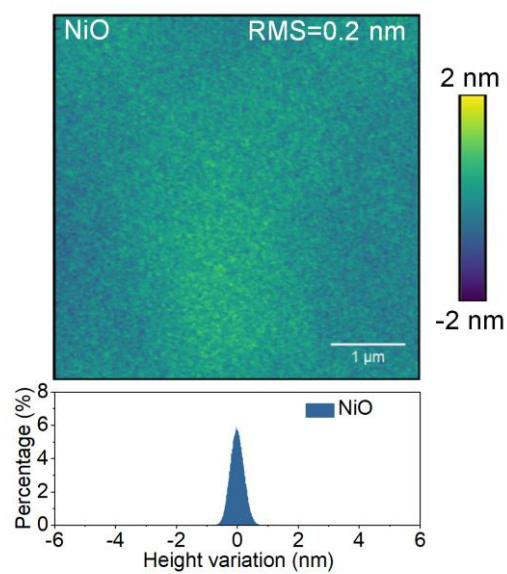
Supplementary Fig. 15 | SEM characterization of SAM layers coated on NiO_x-NPs films. Top-view SEM images of (a) Me-4PACz and (b) Li-Me on NiO_x-NPs films.



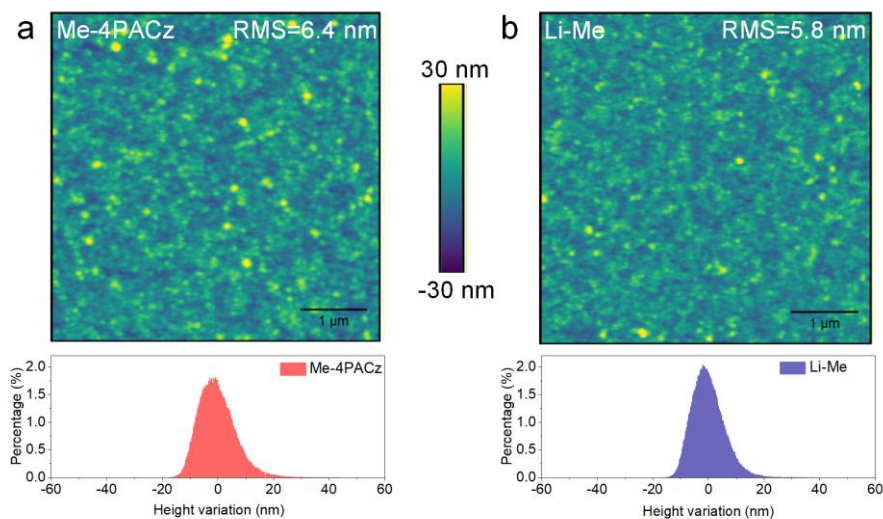
Supplementary Fig. 16 | Elemental mapping of SAM layers coated on NiO_x-NPs films under SEM. Elemental mapping of Ni and P for (a) Me-4PACz and (b) Li-Me modified NiO_x-NPs. The while circles indicate the areas with low density of P.



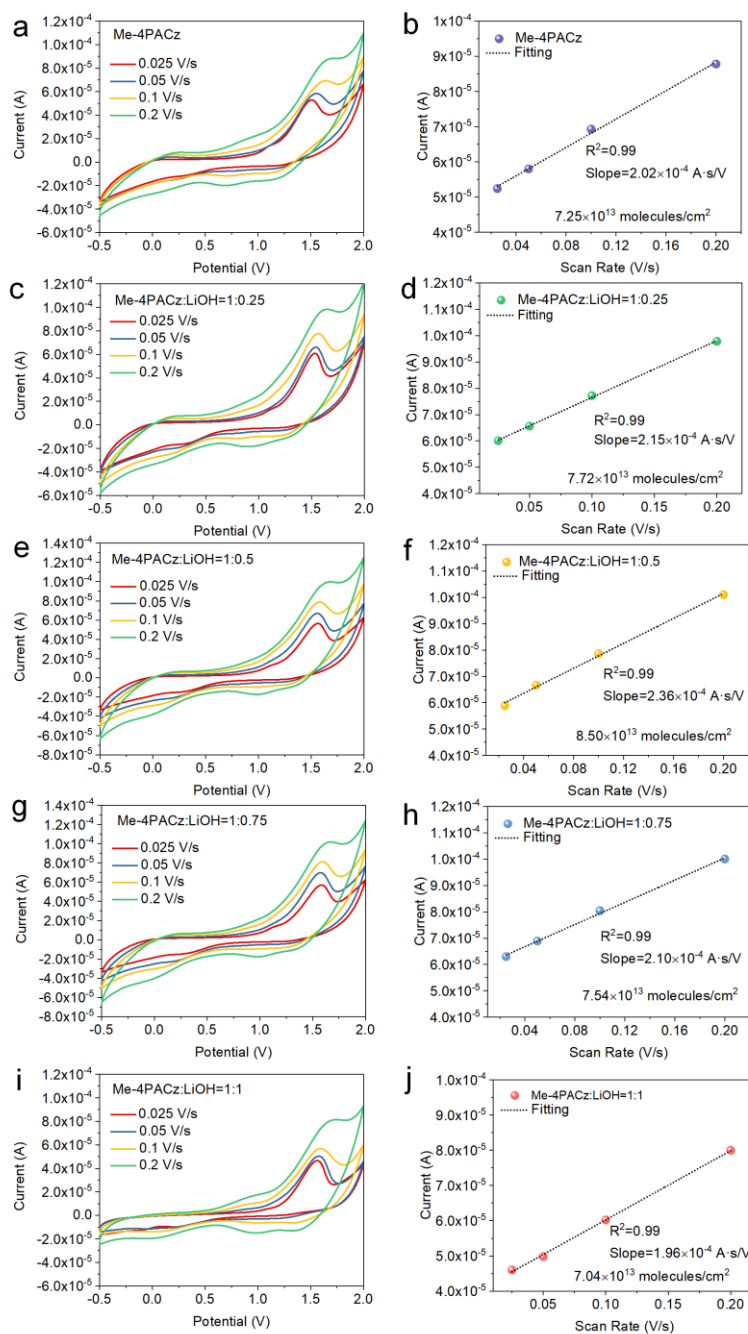
Supplementary Fig. 17 | Element distribution characterized by TOF-SIMS. (a-b) ToF-SIMS depth profiles of PSC devices based on Me-4PACz/ NiO_x -NPs and Li-Me/ NiO_x -NPs. TOF-SIMS signal mapping of (c-d) Li^- of the device based on Me-4PACz and Li-Me (the range is 50 \times 50 μm).



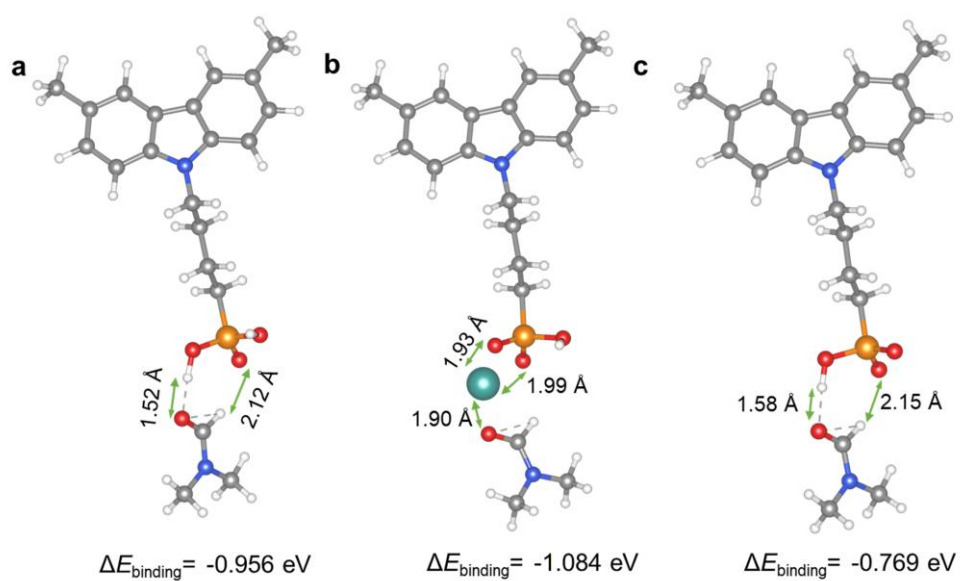
Supplementary Fig. 18 | AFM morphology images and highly statistical distribution of NiO (RMS: root mean square).



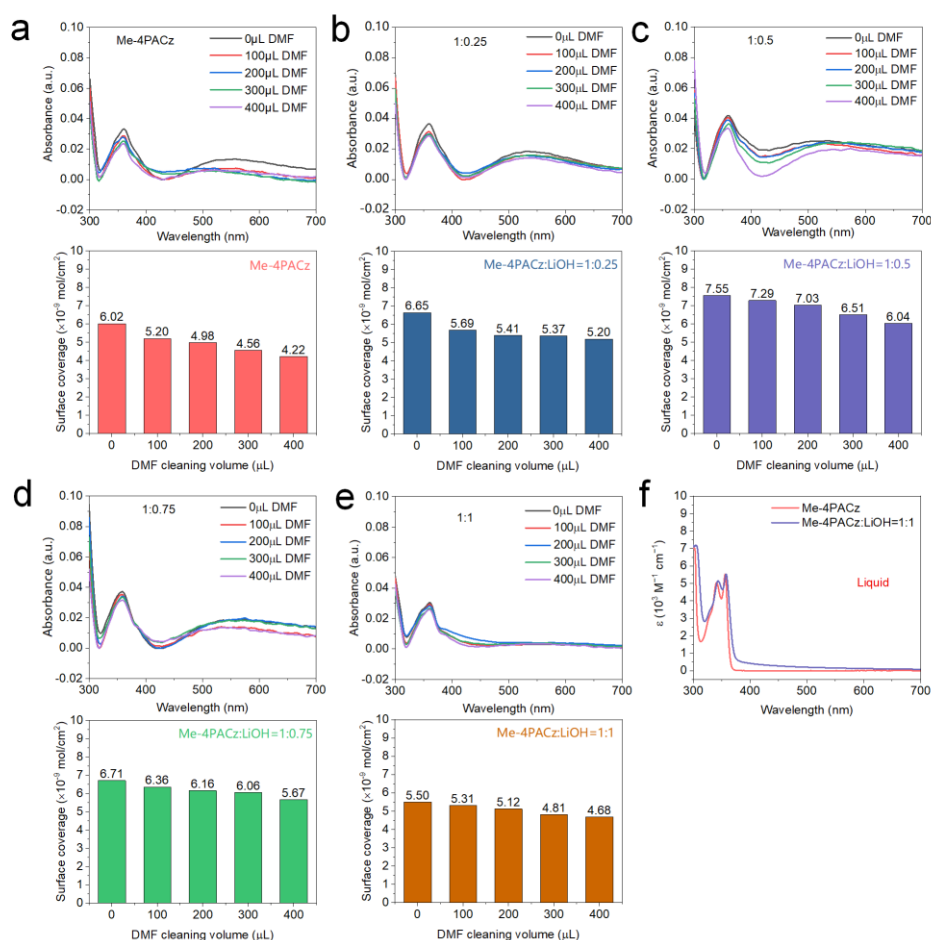
Supplementary Fig. 19 | AFM characterization of SAM layers coated on NiO_x-NPs films. AFM morphology images and highly statistical distribution of (a) Me-4PACz and (b) Li-Me on NiO_x-NPs (RMS: root mean square).



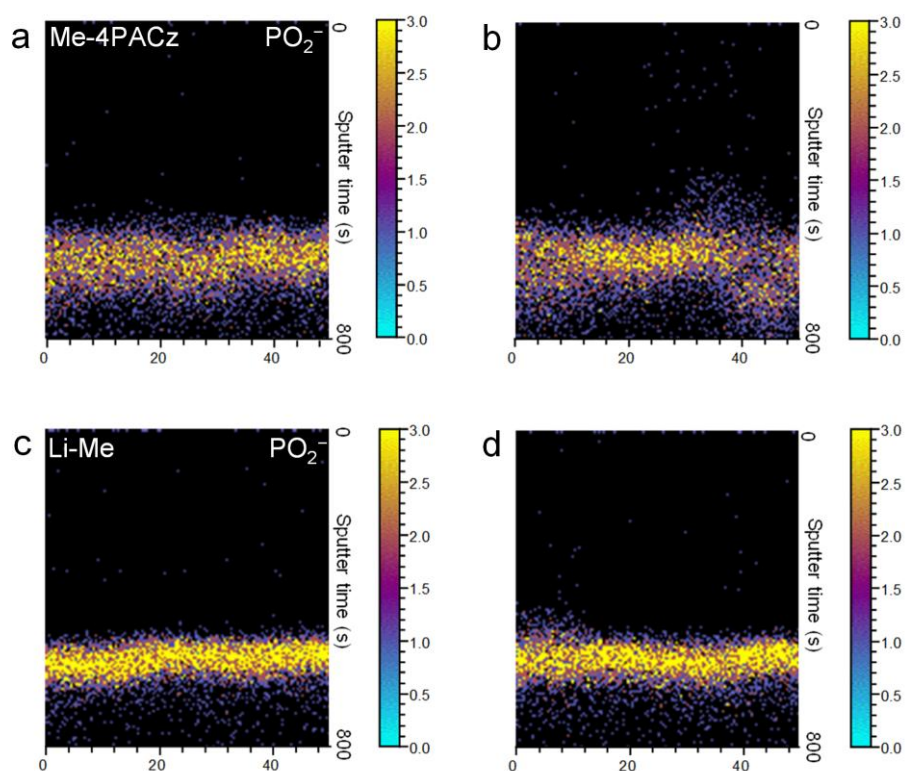
Supplementary Fig. 20 | Cyclic voltammetry (CV) characterization of SAM layers coated on NiO_x-NPs films. Cyclic voltammograms of (a) ITO/NiO_x-NPs/Me-4PACz, (c) ITO/NiO_x-NPs/Me-4PACz:LiOH=1:0.25, (e) ITO/NiO_x-NPs/Me-4PACz:LiOH=1:0.5, (g) ITO/NiO_x-NPs/Me-4PACz:LiOH=1:0.75, and (i) ITO/NiO_x-NPs/Me-4PACz:LiOH=1:1 as the working electrode measured in Ar-saturated o-DCB solution under different voltage scan rates. The relationship between the oxidative peak current and the voltage scan rate for (b) ITO/NiO_x-NPs/Me-4PACz, (d) ITO/NiO_x-NPs/Me-4PACz:LiOH=1:0.25, (f) ITO/NiO_x-NPs/Me-4PACz:LiOH=1:0.5, (h) ITO/NiO_x-NPs/Me-4PACz:LiOH=1:0.75, and (j) ITO/NiO_x-NPs/Me-4PACz:LiOH=1:1 samples. The dashed line represents a linear fit to the raw data.



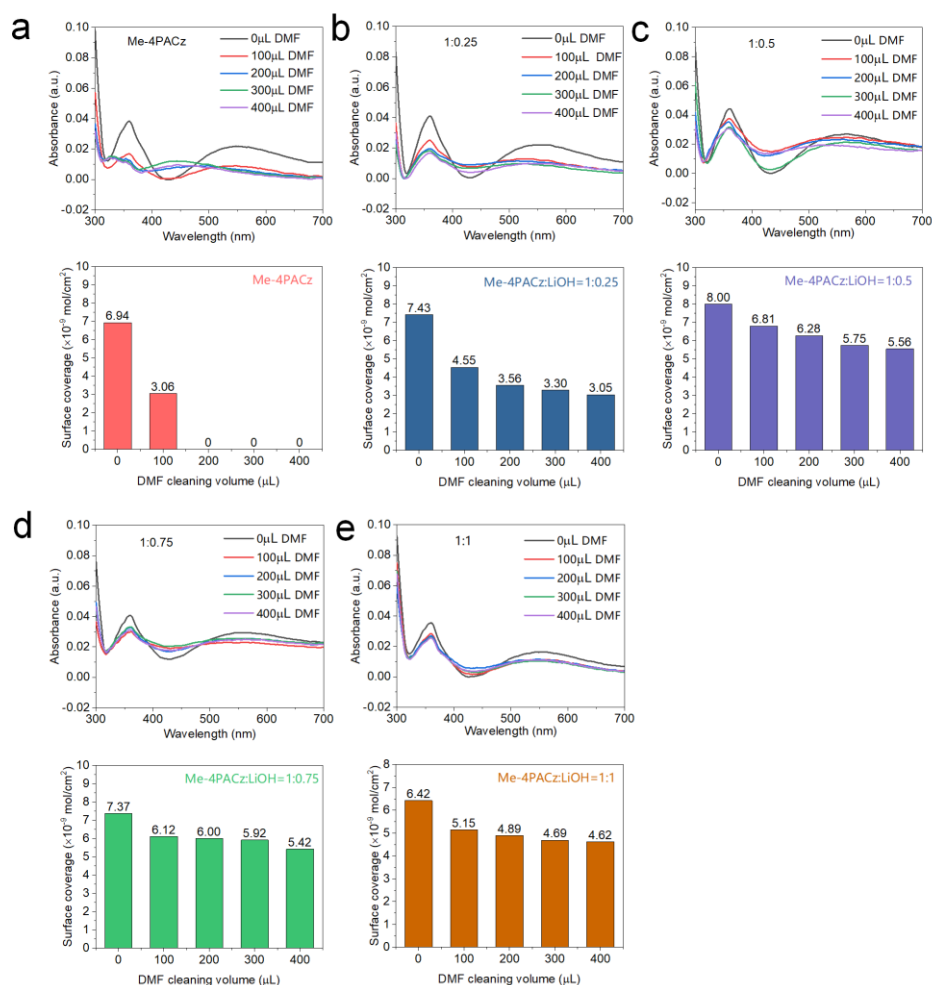
Supplementary Fig. 21 | Binding energy between SAM and DMF molecules. Optimized structure and the calculated bind energy ($\Delta E_{\text{binding}}$) for (a) DMF/Me-4PACz, (b) DMF/Me-4PACz-Li, and (c) DMF/Me-4PACz⁻.



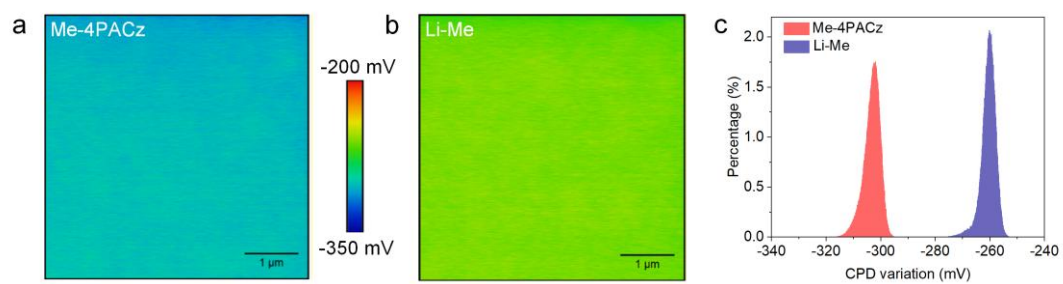
Supplementary Fig. 22 | Changes in the surface coverages of SAMs after DMF washing. (a-e) Top: UV-Vis absorption spectra of different SAMs on NiO_x-NPs films after annealing and then being washed with different amounts of DMF. The absorbance of NiO_x-NPs was subtracted by using a similar NiO_x-NPs substrate. Bottom: SAM density on NiO_x-NPs as a function of DMF washing volume. (f) UV-visible absorption spectra of SAMs (Me-4PACz and Me-4PACz-Li) dissolved in DMF with a concentration of 10^{-5} M.



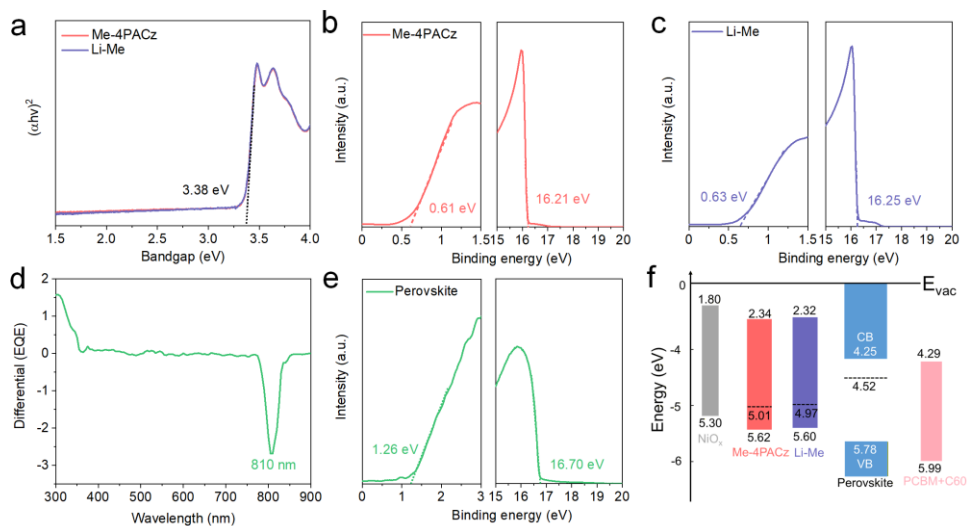
Supplementary Fig. 23 | Distribution of SAMs characterized by TOF-SIMS. (a-b) Cross-sectional TOF-SIMS mapping of Me-4PACz (PO_2^-) in initial and aged PSCs (300 h at 85 °C), respectively. **(c-d)** Cross-sectional TOF-SIMS mapping of Li-Me (PO_2^-) in initial and aged PSCs (300 h at 85 °C), respectively (the range is 50 μm).



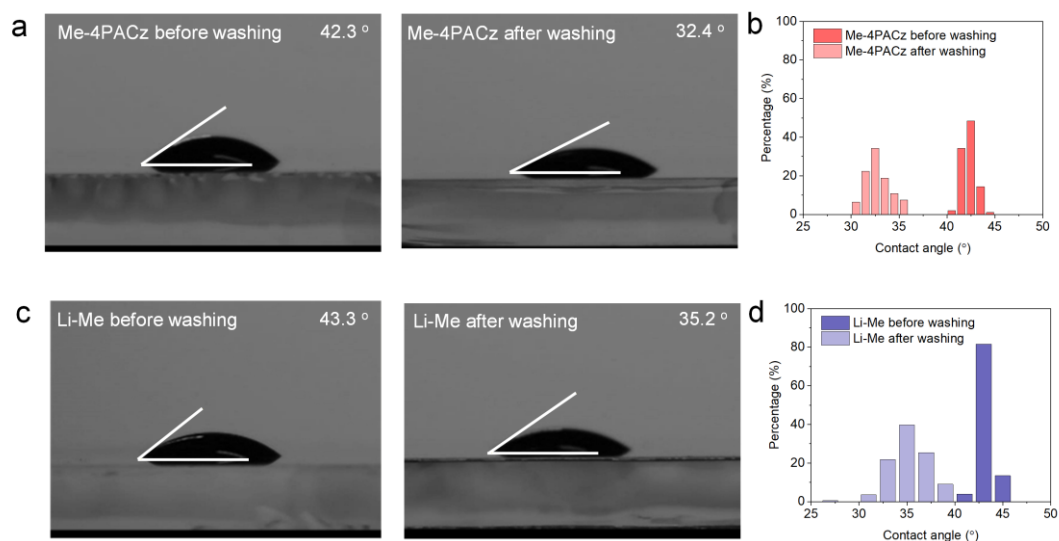
Supplementary Fig. 24 | Changes in the surface coverages of SAMs after DMF washing. (a-e) Top: UV-Vis absorption spectra of SAMs on NiO_x-NPs without annealing and being washed with different amounts of DMF. Bottom: Variation in SAM densities on NiO_x-NPs as a function of DMF washing volume.



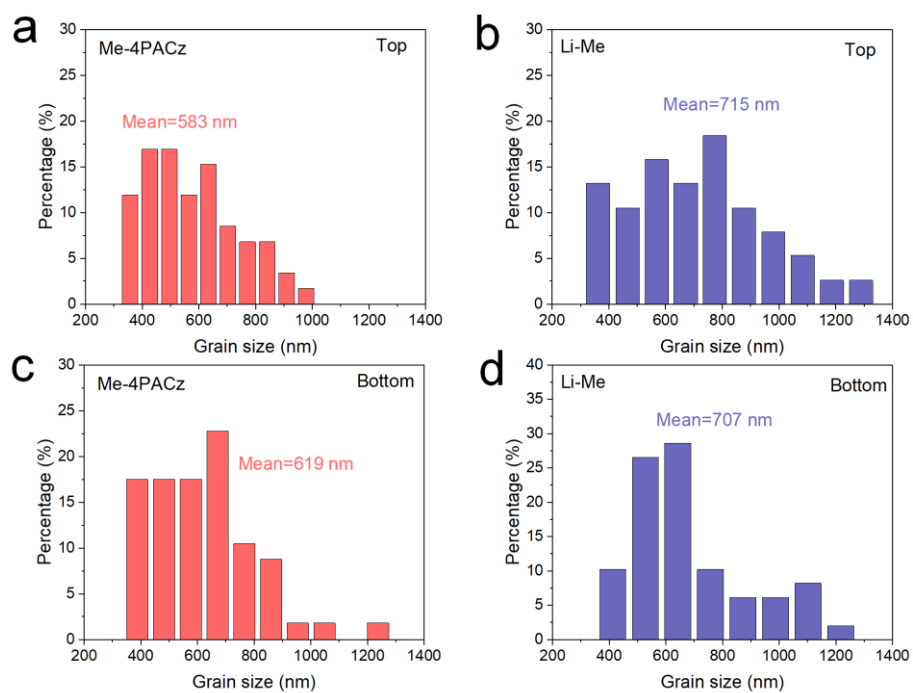
Supplementary Fig. 25 | KPFM characterization of SAM layers. KPFM images of (a) NiO_x-NPs/Me-4PACz and (b) NiO_x-NPs/Li-Me. (c) Potential statistical distribution in KPEM.



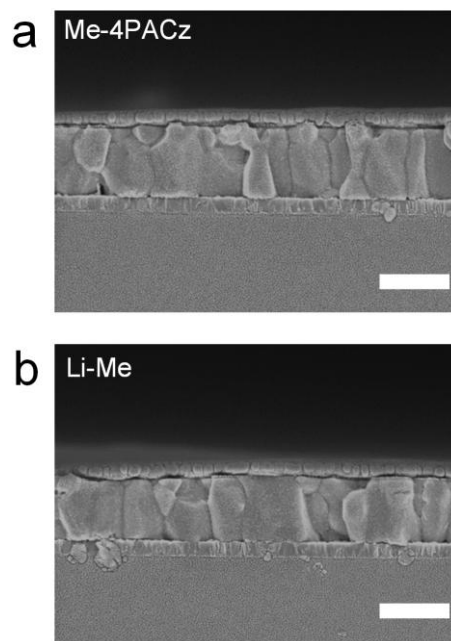
Supplementary Fig. 26 | The characterization of energy levels of SAMs. (a) Tauc-plot curves of Me-4PACz and Li-Me ethanol solutions. UPS data of (b) NiO_x-NPs/Me-4PACz and (c) NiO_x-NPs/Li-Me. (d) d(EQE)/dE versus wavelength confirming the bandgap. (e) UPS data of perovskite film. (f) Functional layer band structure (E_{vac} , vacuum level; CB, conduction band; VB, valence band).



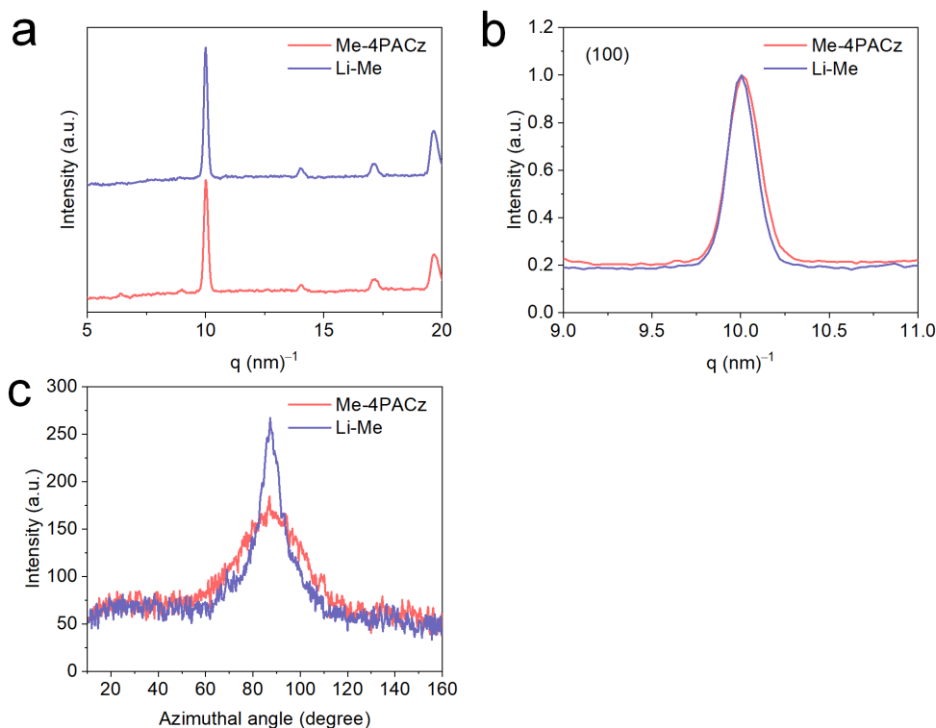
Supplementary Fig. 27 | The contact angle of a perovskite precursor on different SAM surfaces. (a) Me-4PACz/NiO_x-NPs and (c) Li-Me/NiO_x-NPs. Statistical analysis of contact angles on the surfaces of (b) Me-4PACz/NiO_x-NPs and (d) Li-Me/NiO_x-NPs.



Supplementary Fig. 28 | Statistical distribution of perovskite grain sizes. Histogram distribution of (a-b) surface and (c-d) bottom perovskite films on Me-4PACz/NiO_x-NPs and Li-Me/NiO_x-NPs layers.

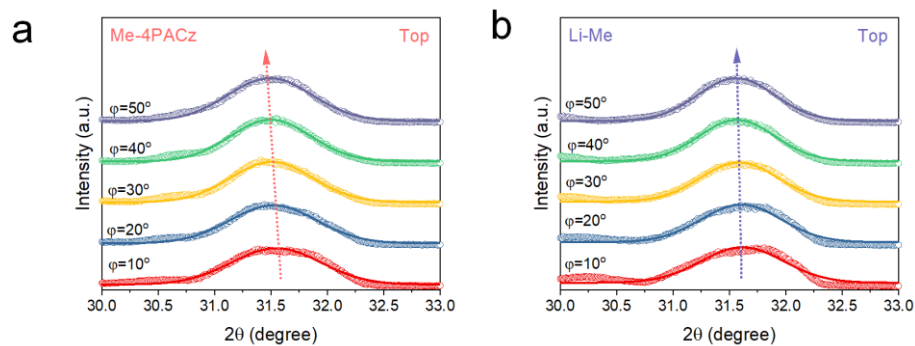


Supplementary Fig. 29 | Cross-sectional SEM. (a-b) Cross-sectional views of devices on two different SAMs. The scales in all images are 1 μm .

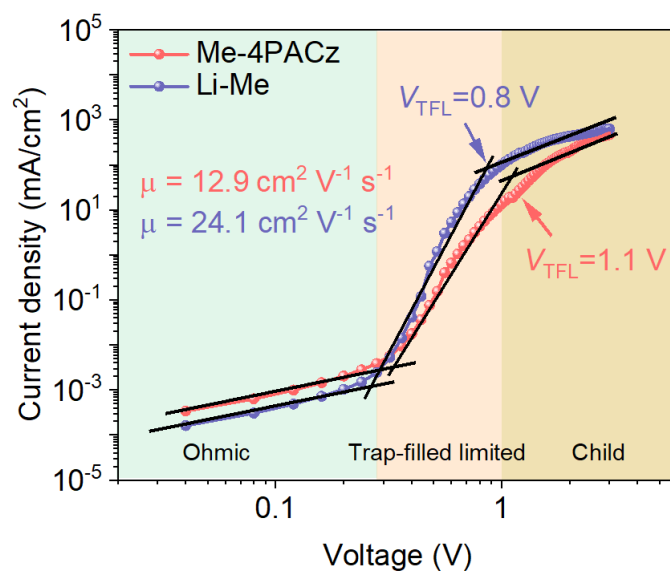


Supplementary Fig. 30 | Crystal orientation analysis of perovskite films. (a) Circular average diffraction pattern of perovskite films deposited on Me-4PACz/ NiO_x -NPs and Li-Me/ NiO_x -NPs. (b) The full width at half maximum (FWHM) of the (100) peak. (c) Radially integrated intensity plots along the ring at $q = 10 \text{ nm}^{-1}$, assigned to the (100) plane of the perovskite films on Me-4PACz/ NiO_x -NPs and Li-Me/ NiO_x -NPs.

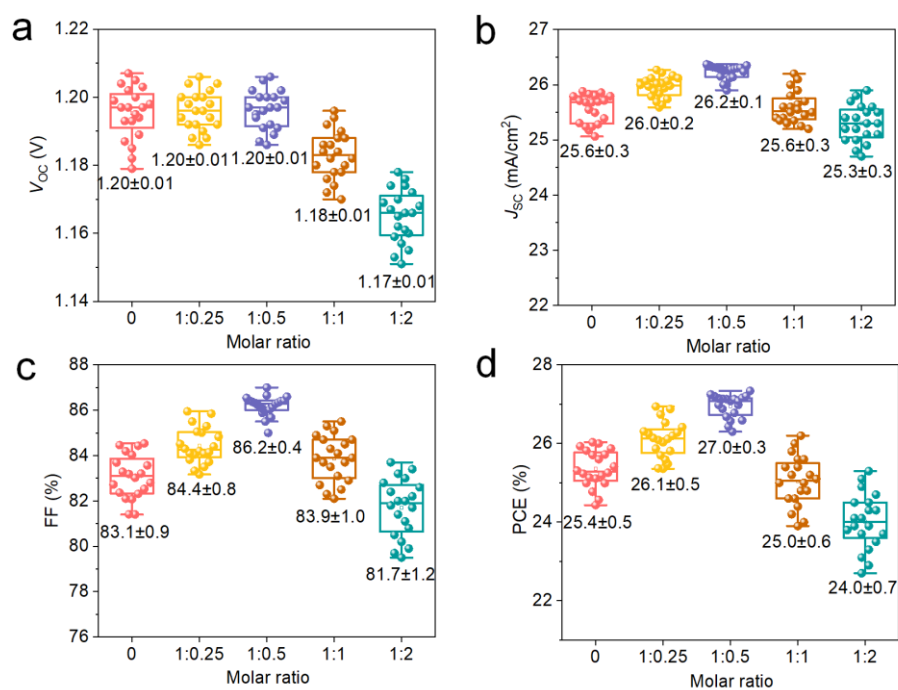
The crystallinity of perovskite films was evaluated by GIWAXS. The diffraction ring in GIWAXS at q values of 10 nm^{-1} corresponds to (100) plane of perovskite. The half-peak width of the (100) plane of the Li-Me based perovskite film is narrower than that of the Me-4PACz based film, indicating enhanced perovskite crystallinity (**Supplementary Fig. 30a-b**). Moreover, The Debye-Scherrer rings of the (100) plane of Li-Me based perovskite film shows sharper diffraction signals, suggesting that the crystal packing is better oriented with a dominant out-of-plane orientation (**Supplementary Fig. 30c**)



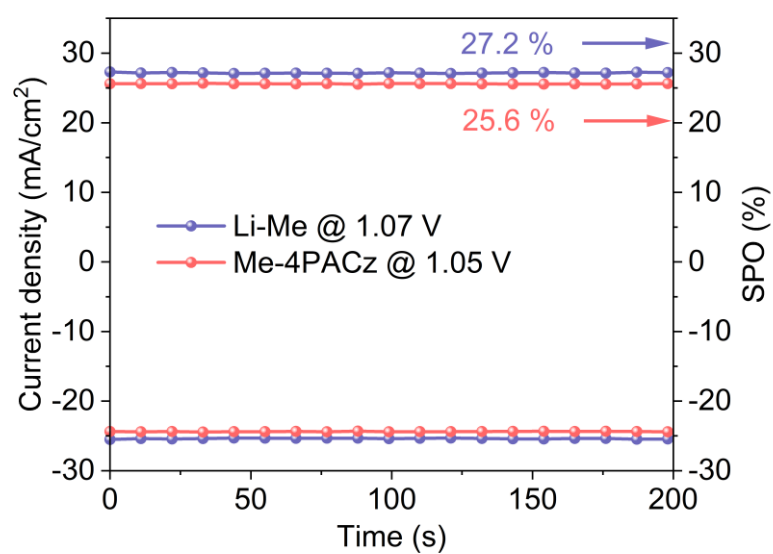
Supplementary Fig. 31 | GIXRD characterization of perovskite films. GIXRD with different ϕ angles (10°-50°) for perovskite films deposited on (a) Me-4PACz/NiO_x-NPs and (b) Li-Me/NiO_x-NPs.



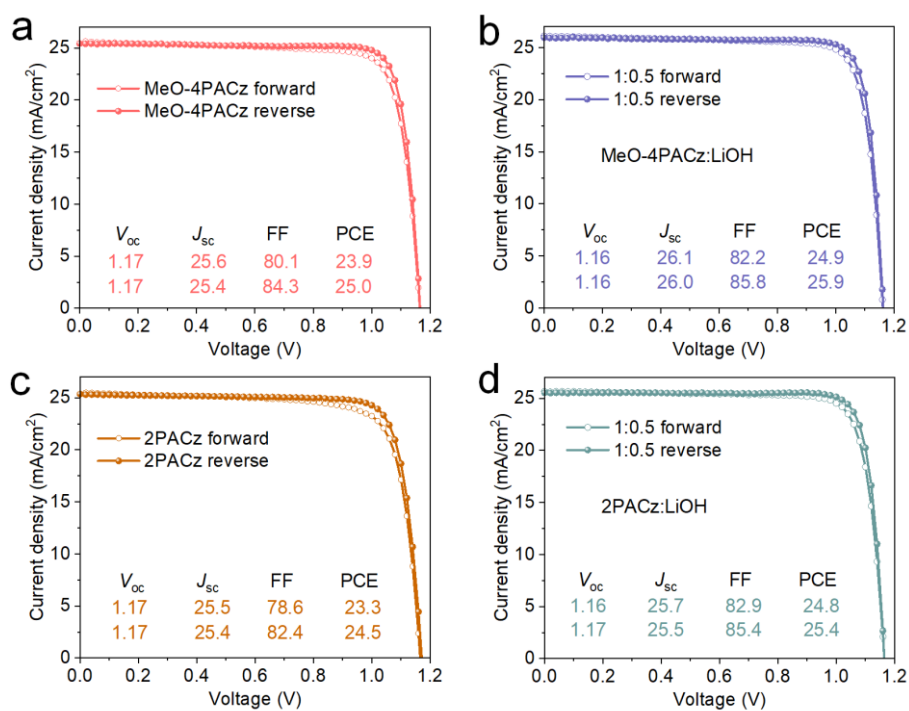
Supplementary Fig. 32 | SCLC of the hole-only perovskite devices prepared on different SAM layers.



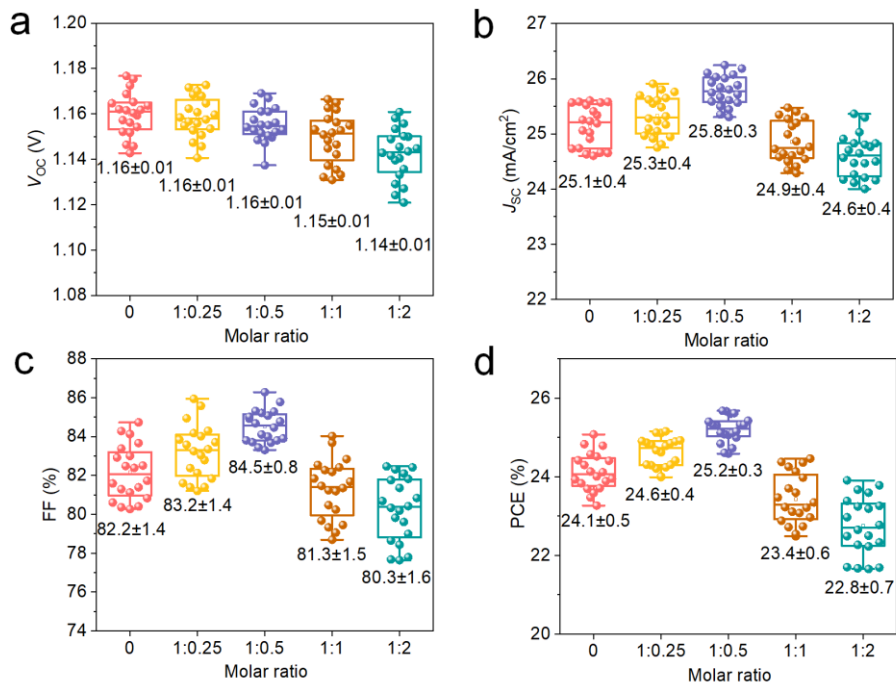
Supplementary Fig. 33 | Statistics of photovoltaic parameters of PSCs. (a-d) Photovoltaic parameters distribution of V_{oc} , J_{sc} , FF, and PCE obtained from 20 devices with various molar ratio of LiOH-reacted Me-4PACz.



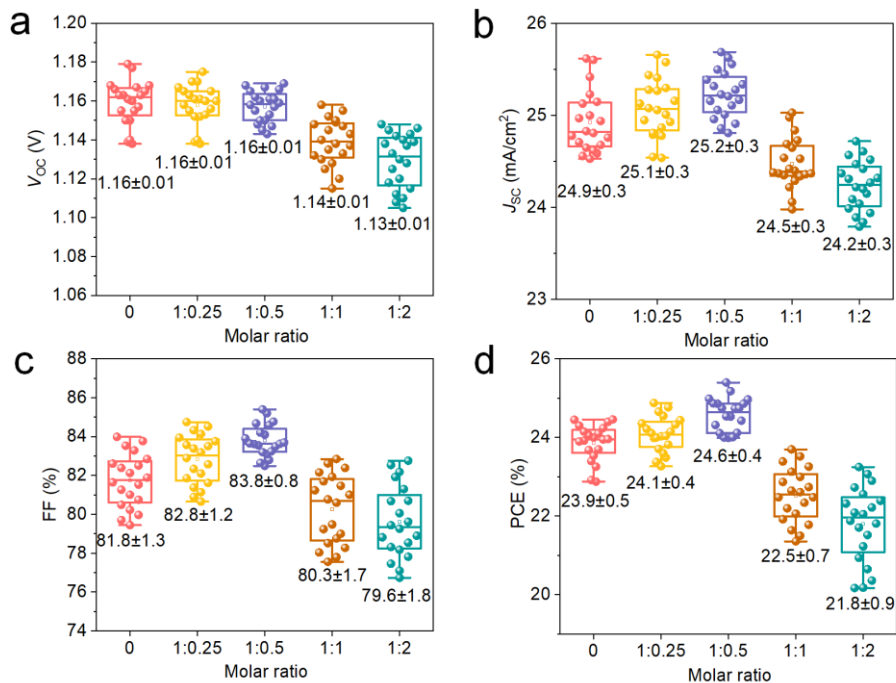
Supplementary Fig. 34 | Steady-state power output (SPO) of PSCs.



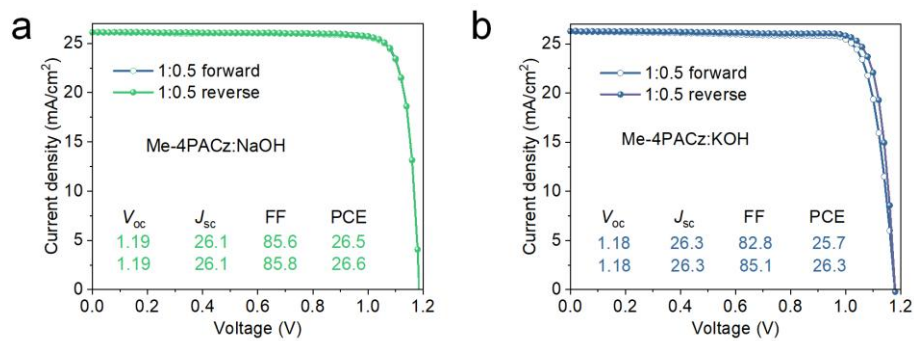
Supplementary Fig. 36 | Photovoltaic performance of PSCs prepared on different SAMs. (a) J - V curves of a device based on NiO_x -NPs/MeO-4PACz HTL. (b) J - V curves of a device based on a HTL of NiO_x -NPs/MeO-4PACz:LiOH=1:0.5. (c) J - V curves of a device based on a HTL of NiO_x -NPs/2PACz. (d) J - V curves of a device based on a HTL of NiO_x -NPs/2PACz:LiOH=1:0.5.



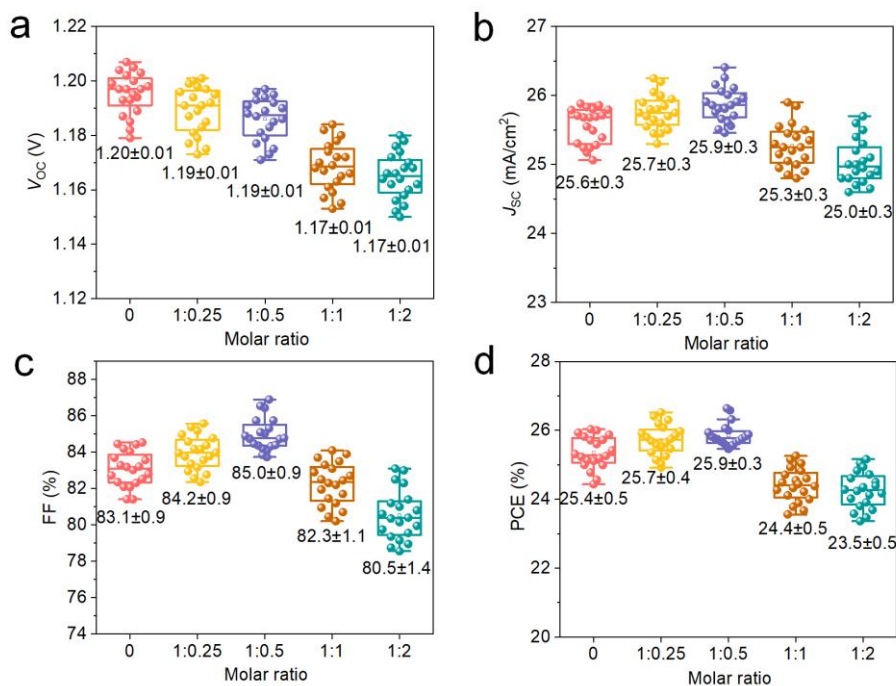
Supplementary Fig. 37 | Statistics of photovoltaic parameters of PSCs. (a-d) The distribution of photovoltaic parameters (V_{oc} , J_{sc} , FF, and PCE) obtained from 20 devices with various molar ratios of MeO-4PACz : LiOH.



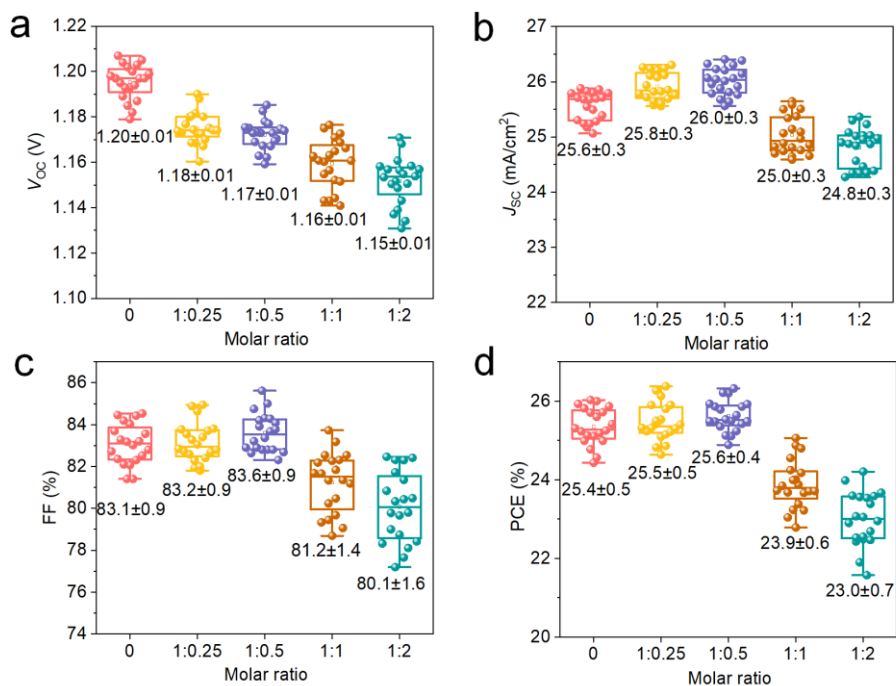
Supplementary Fig. 38 | Statistics of photovoltaic parameters of PSCs. (a-d) The distribution of photovoltaic parameters (V_{oc} , J_{sc} , FF, and PCE) obtained from 20 devices with various molar ratios of 2PACz : LiOH.



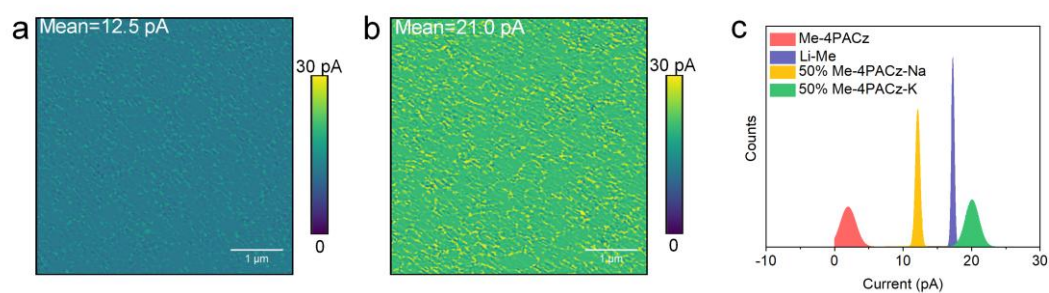
Supplementary Fig. 39 | Changes in the photovoltaic performance induced by other alkali treatments for Me-4PACz. (a) J - V curves of a device based on a HTL of NiO_x -NPs/Me-4PACz:NaOH=1:0.5. (b) J - V curves of a device based on a HTL of NiO_x -NPs/Me-4PACz:KOH=1:0.5.



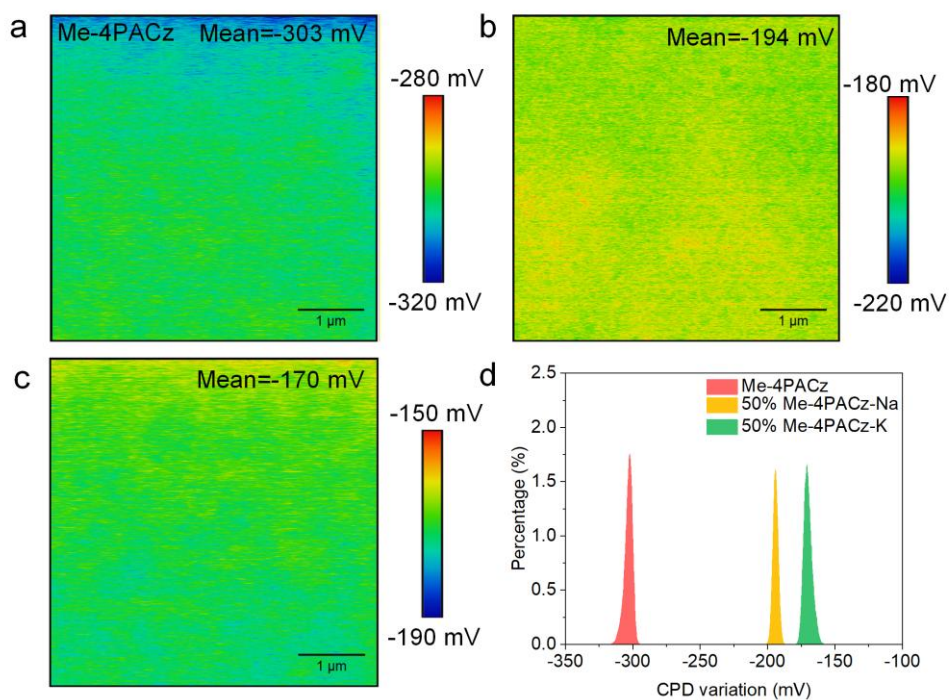
Supplementary Fig. 40 | Statistics of photovoltaic parameters of PSCs. (a-d) Photovoltaic parameters (V_{oc} , J_{sc} , FF, and PCE) obtained from 20 devices with various molar ratios of Me-4PACz : NaOH.



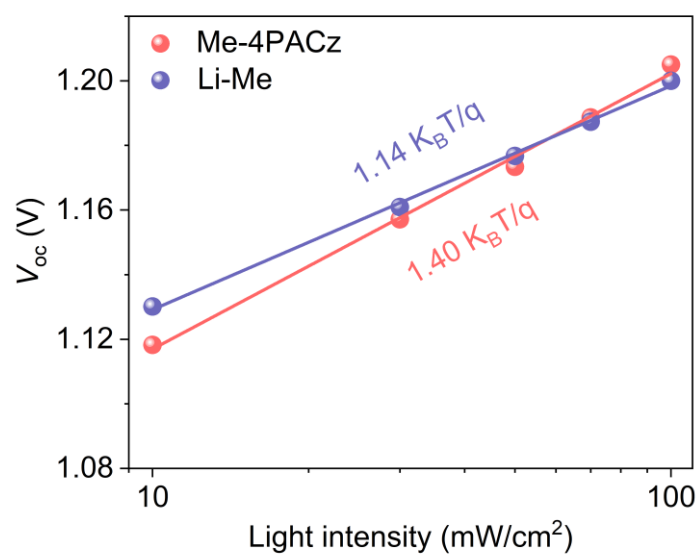
Supplementary Fig. 41 | Statistics of photovoltaic parameters of PSCs. (a-d) Photovoltaic parameters (V_{oc} , J_{sc} , FF, and PCE) obtained from 20 devices with various molar ratios of Me-4PACz : KOH.



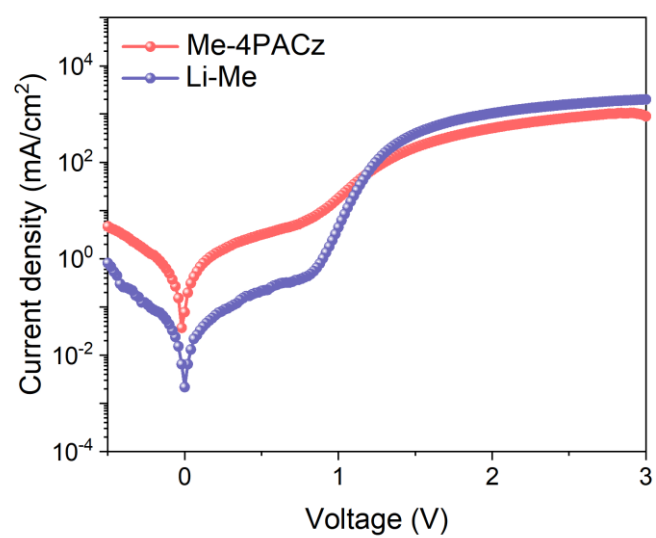
Supplementary Fig. 42 | C-AFM images of SAM layers on NiO_x-NPs/ITO surfaces. C-AFM imaging of (a) 50% Me-4PACz-Na and (b) 50% Me-4PACz-K under a bias voltage of +500 mV. (c) Current statistical distribution in C-AFM.



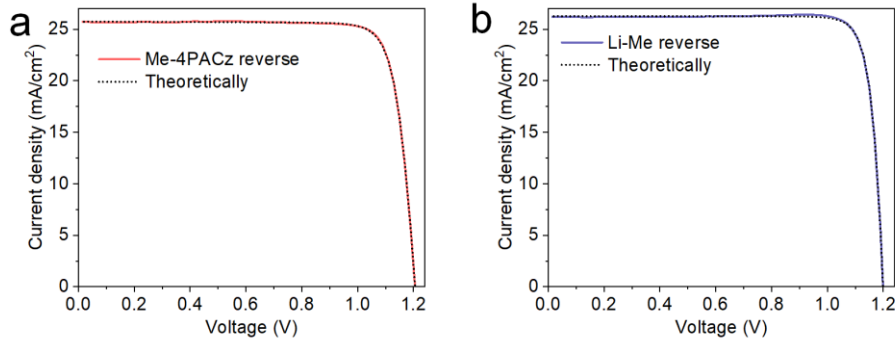
Supplementary Fig. 43 | KPFM characterization of SAM layers. KPFM images of (a) NiO_x-NPs/Me-4PACz, (b) NiO_x-NPs/50% Me-4PACz-Na, and (c) NiO_x-NPs/50% Me-4PACz-K. (d) Potential statistical distribution in KPFM.



Supplementary Fig. 44 | Variation of V_{oc} in PSCs with changing light intensity.



Supplementary Fig. 45 | Dark J - V curves of PSCs based on different SAM layers.



Supplementary Fig. 46 | The comparison of J - V curves between theoretical simulation and experimental measurement. Theoretically fitted J - V curves by modified detailed balance model and experimentally measured J - V characteristics for the PSCs based on (a) Me-4PACz/NiO_x-NPs and (b) Li-Me/NiO_x-NPs.

In order to understand the loss mechanism and qualify loss proportions (loss factors) of FF, the revised detailed balance model is used

$$J = \frac{V - JR_s}{R_{sh}} + J_n(V - JR_s) + J_r(V - JR_s) - J_p$$

where V is the applied voltage, J_p is the photocurrent, J_r and J_n are the current loss due to the radiative bimolecular emission and the nonradiative defect-induced recombination, respectively. R_s is the series resistance, which describes the ohmic loss by the contacts, carrier transport layers, and the hetero-junction interfaces between the perovskite and carrier transport layers. The defects, pinholes and voids induced current leakage is represented by the shunt resistance R_{sh} .

The photocurrent is given by

$$J_p = q \int_0^\infty \alpha(\lambda, L) \frac{\Gamma(\lambda)\lambda}{hc_0} d\lambda$$

where c_0 is the speed of light in air, Γ is the AM 1.5 G spectrum of Sun, λ is the wavelength and q is the elementary charge. The absorptivity α is the ratio of power absorbed by the perovskite active layer over the power of incident Sunlight. It can be obtained by numerically solving Maxwell equation. The refractive indices of materials can be obtained by ellipsometer measurement.

The radiative current is written as

$$J_r(V - JR_s) = J_0^r \left[\exp\left(\frac{q(V - JR_s)}{k_B T}\right) - 1 \right]$$

where k_B is the Boltzmann constant and T is the Kelvin temperature. Here, the radiative saturation current J_0^r is of the form

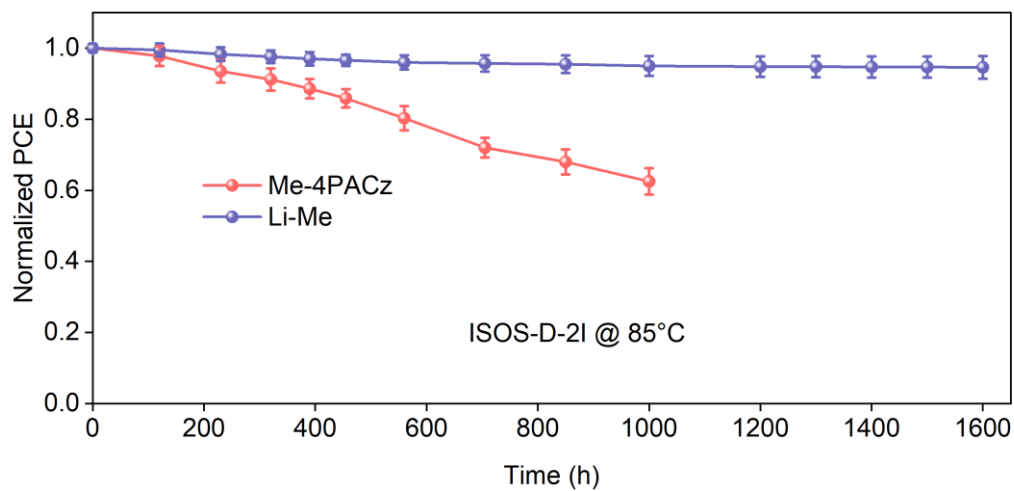
$$J_0^r = q \int_0^\infty \alpha(\lambda, L) \frac{\Gamma_0(\lambda)\lambda}{hc_0} d\lambda$$

It is proportional to the spectral overlap integral between the absorptivity α and black-body (thermal) emission spectrum Γ_0 at room temperature ($T=300$ K).

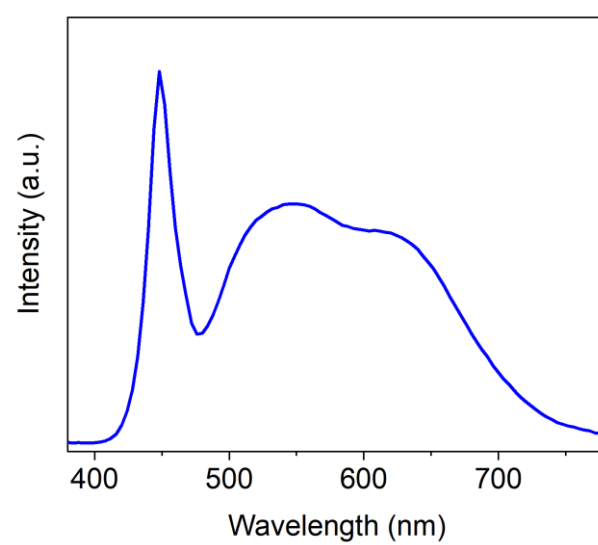
For perovskite solar cells, the dominant nonradiative recombination is the defect-induced recombination. Thus, the nonradiative current reads

$$J_n(V - JR_s) = J_0^n \exp\left(\frac{q(V - JR_s)}{2k_B T}\right), \quad J_0^n = qn_i\gamma_b L + qn_i\gamma_s = qn_i\gamma$$

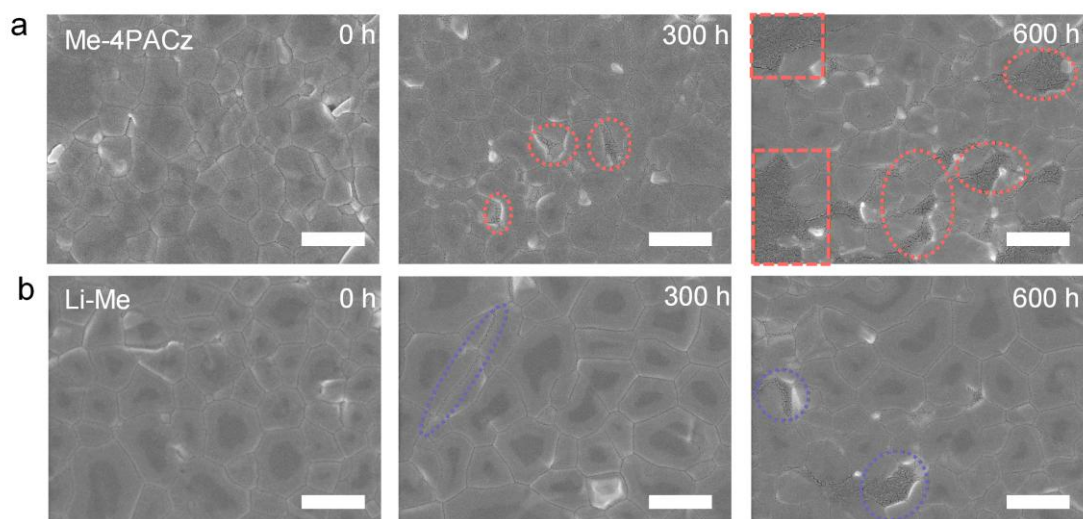
where γ_b and γ_s are the bulk nonradiative recombination rate and surface one, respectively, L is the perovskite active layer thickness, and n_i is the intrinsic carrier density of the perovskite material.



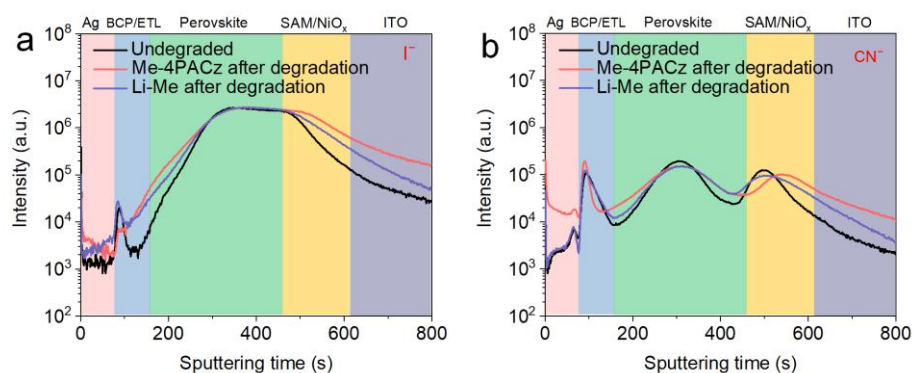
Supplementary Fig. 47 | Thermal stability of the PSCs based on Me-4PACz/NiO_x-NPs and Li-Me/NiO_x-NPs at 85 °C (the average PCE is obtained from 10 devices of each type of device, and the error bars represent the standard deviation of the devices).



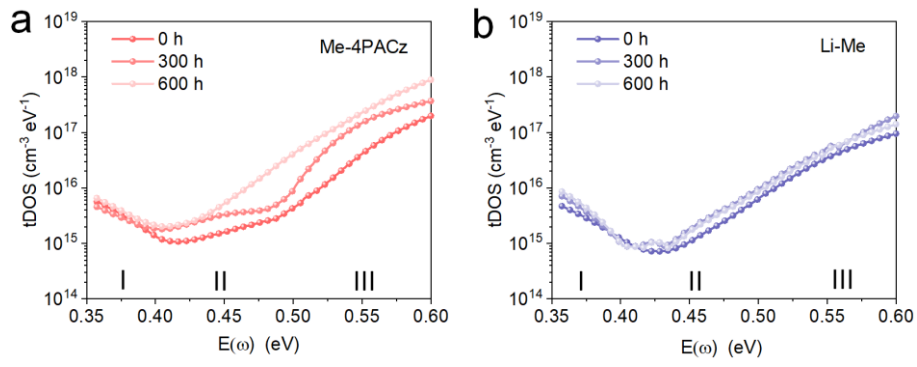
Supplementary Fig. 48 | The light spectra of the LED lamp used for MPP tracking stability tests.



Supplementary Fig. 49 | Changes of perovskite bottom surface morphology with heating time. Morphology of the perovskite bottom on (a) Me-4PACz/NiO_x-NPs and (b) Li-Me/NiO_x-NPs before and after aging at 85 °C for different periods of time (the scale is 1 μm and the dashed area represents the amorphous region).



Supplementary Fig. 50 | Ion migration of perovskite films after degradation. (a-b) TOF-SIMS depth profiles of PSC devices based Me-4PACz and Li-Me before and after thermal aging at 85°C for 300 hours in N₂ atmosphere. I⁻ and CN⁻ (FA⁺, MA⁺) are selected for following the evolution of the perovskite film.



Supplementary Fig. 51 | Defect density versus aging time. Trap density of (a) NiO_x-NPs/Me-4PACz and (b) NiO_x-NPs/Li-Me -based PSCs heated at 85 °C for different periods.

Supplementary Table 1. The fitting parameters for the TRPL curves of perovskite films coated on Me-4PACz and Li-Me.

Sample	τ_1 [μ s]	A_1	τ_2 [μ s]	A_2	τ_{ave} [μ s]
Me-4PACz	0.31	0.28	1.65	0.41	1.50
Li-Me	0.24	0.36	2.78	0.31	2.55

$$\tau_{ave} = \frac{A_1\tau_1^2 + A_2\tau_2^2}{A_1\tau_1 + A_2\tau_2}$$

Supplementary Table 2. Surface densities of SAM molecules and resultant PCEs of PSCs.

Materials/Methods	Control (molecules/cm ²)	After modification (molecules/cm ²)	Surface density variation	PCE	Certified PCE	Year/Ref.
4PATTI-C3/ 4PATTI-C4	9.00×10 ¹²	9.63×10 ¹²	7.00%	21.7%	N.A.	2024 ¹⁸
3PATAT-C3/ MeO-2PACz	1.60×10 ¹³	1.00×10 ¹³	-37.5%	23.0%	N.A.	2023 ¹⁹
CbzNaph solution	2.48×10 ¹³	3.84×10 ¹³	54.84%	24.98%	N.A.	2023 ²⁰
2PACz+3-MPA	2.3×10 ¹³	3.9×10 ¹³	69.57%	25.3%	24.8%	2023 ⁷
Py3/2PACz	3.39×10 ¹⁵	3.31×10 ¹⁵	-2.36%	26.1%	25.7%	2024 ²¹
Li-Me/Me- 4PACz	7.25×10 ¹³	8.50×10 ¹³	17.24%	27.3%	27.3%	This Work

Supplementary Table 3. Comparison of the operational stability of PSCs.

Device structure	Champion PCE (certified PCE)	Light source	Ageing condition	PCE _t /PCE ₀ *	Reference
ITO/perovskite+DMAcPA/PCBM/ BCP/Ag	25.9% (25.4%)	White LED	Air, 50% RH, 25 °C, 1000 h	96.6%	Nature, 2023 ²²
ITO/NiO _x /MeO-4PADBC /perovskite/C60/BCP/Ag	25.6% (25.6%)	White LED	N ₂ , 65 °C, 1200 h	90%	Science, 2023 ²³
FTO/Ph-4PACz /perovskite/C60/BCP/Ag	25.2% (24.4%)	White LED	N ₂ , 85% RH, 600 h	100%	Nat. Photonics, 2024 ²⁴
ITO/Me-4PACz /perovskite/C60/BCP/Ag	24.5% (N.A.)	White LED	N ₂ , 40-45 °C, 1200 h	91%	Nat. Energy, 2023 ²⁵
ITO/2PACz/perovskite/C60/BCP/ Cu	25.1% (24.7%)	White LED	Air, 60±10% RH, 25±5 °C, 1000 h	90%	Nat. Commun., 2024 ⁸
ITO/DC-TMPS /perovskite/PEAI/C60/ZnO/Au	24.8% (24.6%)	Xenon lamp	85 °C, 1200 h	98.2%	Science, 2024 ²⁶
ITO/Py3/perovskite/OAmI/LiF/C6 0/BCP/Ag	26.1% (25.7%)	White LED	55 °C, 600 h	99%	Nature, 2024 ²¹
ITO/NiO _x /Me-PhPACz /perovskite/C60/BCP/Cu	26.2% (26.1%)	White LED	N ₂ , 50±10 °C, 3000 h	95.09%	Joule, 2024 ²⁷
ITO/NiO _x /Me-4PACz /perovskite/PCBM/SnO ₂ /ITO/Cu	25.5% (25.2%)	White LED	50 °C, 1000 h	85.4%	Science, 2023 ²⁸
ITO/2PACz+Me-4PACz /perovskite/C60/SnO ₂ /Ag	26.9 (26.2%)	White LED	Air, 50% RH, 65 °C, 1200 h	95%	Science, 2024 ²⁹
ITO/GM-4PACz /perovskite/PCBM/BCP/Ag	25.5% (N.A.)	White LED	Air, 30±5% RH, 25 °C, 1000 h	91.75%	Angew. Chem. Int. Ed., 2024 ³⁰
ITO/NiO _x /perovskite/C60/BCP/Ag	26.7 (26.1%)	White LED	1000 h	80%	Adv Mater., 2024 ³¹
ITO/Me-4PACz+MeO-2PACz /perovskite/CPMAC/ALD- SnO _x /Ag	26.1% (N.A.)	N.A.	N ₂ , 65 °C, 2100 h	97.6%	Science, 2025 ³²
ITO/PTAA/perovskite/CPMAC/A LD-SnO _x /Ag			N ₂ , 85 °C, 1500 h	95.0%	
ITO/2PACz/perovskite/PMMA/gra phene/PC61BM/BCP/Au	24.6% (N.A.)	White LED	N ₂ , 90 °C, 3670 h	97.3%	Science, 2025 ³³
ITO/PTAA/MoS ₂ /perovskite/MoS ₂ /C60/BCP/Ag	26.2% (25.9%)	N.A.	Air, 85 °C, 1200 h	>96%	Science, 2025 ³⁴
ITO/PTAA/perovskite/C60/SnO ₂ /I TO/Au	23.1% (N.A.)	Metal-Halide Lamps	N ₂ , 85 °C, 622 h	99%	Science, 2025 ³⁵
ITO/MPA-CPA /perovskite/Nd@C ₈₂ /C60/BCP/Ag	26.8% (26.3%)	White LED	Air, 50% RH, 65 °C, 2500 h	82%	Nature, 2025 ³⁶
ITO/NiO _x /Li- Me/perovskite/C60/BCP/Cr/Au	27.3% (27.3%)	White LED	Air, 50% RH, 65 °C, 2000 h Air, 50% RH, 85 °C, 1000 h	94.5% 93.3%	This work

[*] PCE₀ and PCE_t are the efficiencies of devices before and after stability tests.

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- 2 Neese, F. *et al.* The ORCA quantum chemistry program package. *J. Chem. Phys.* **152**, 224108, (2020).
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